10/519699

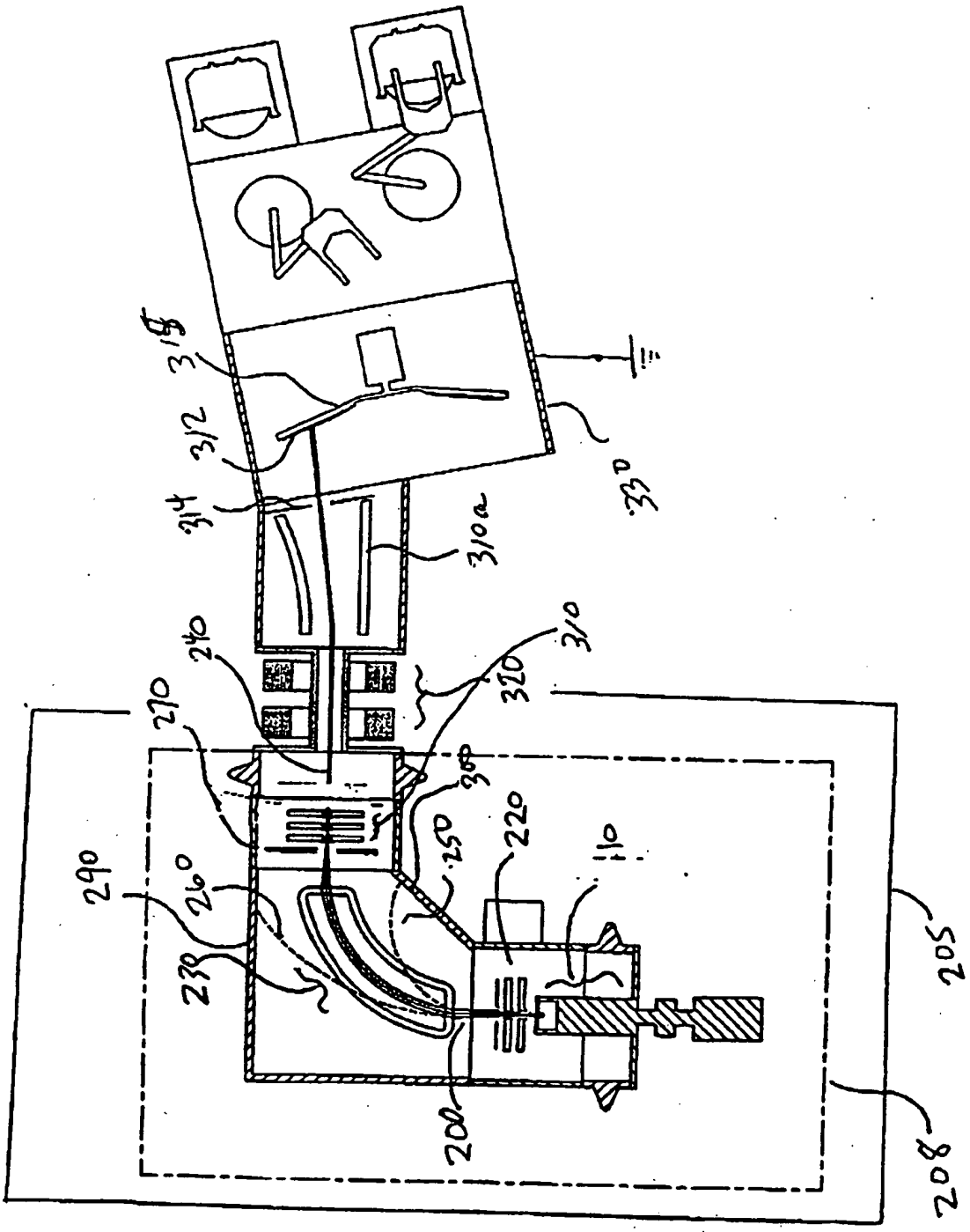


Fig. 1A

10/519699

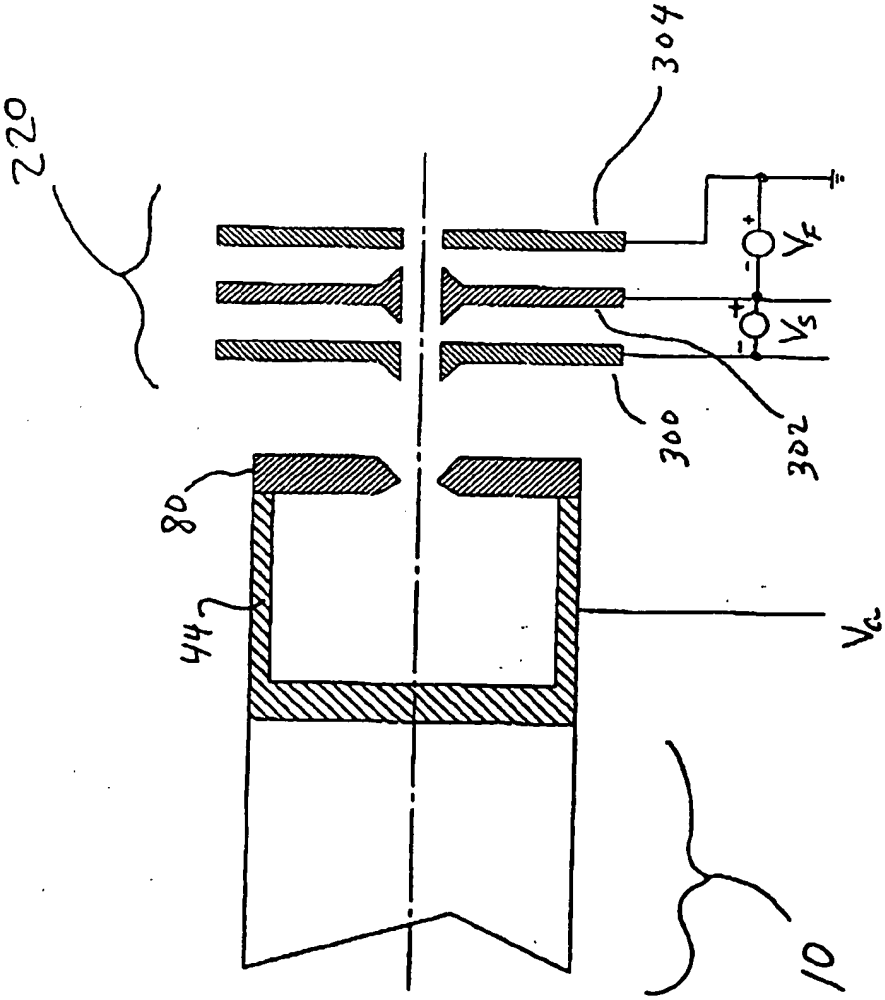


Fig. 1B

10/519699

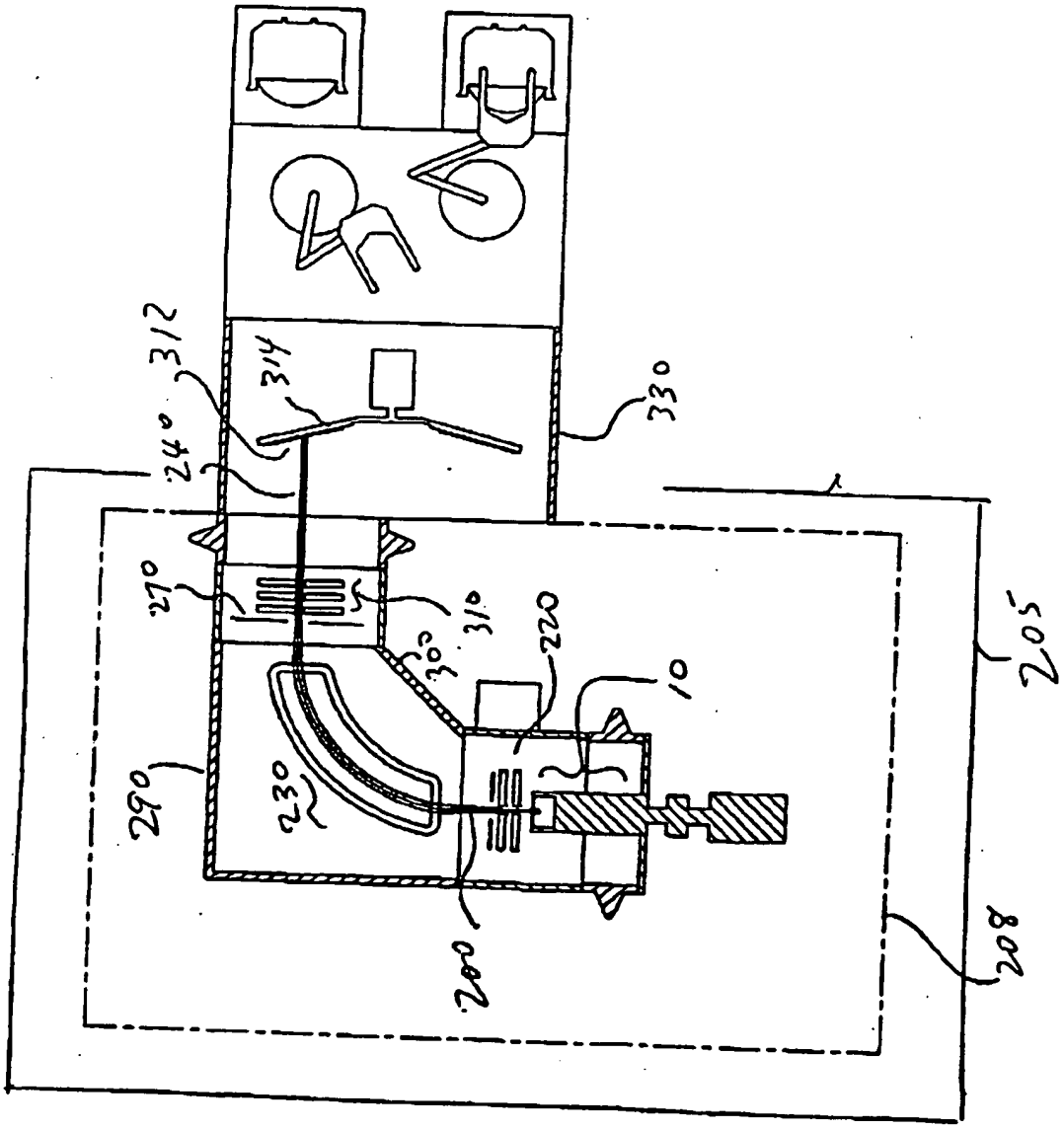


Fig. 1C

10/519699

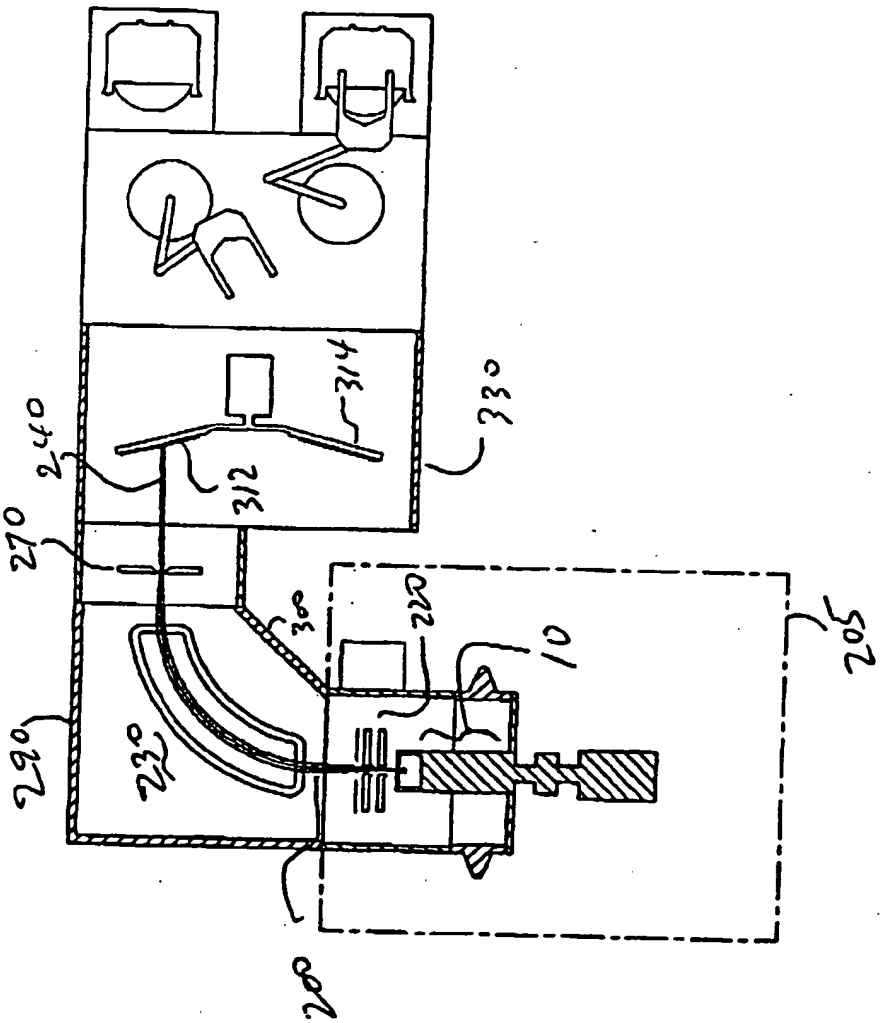


Fig. 1D

10/519699

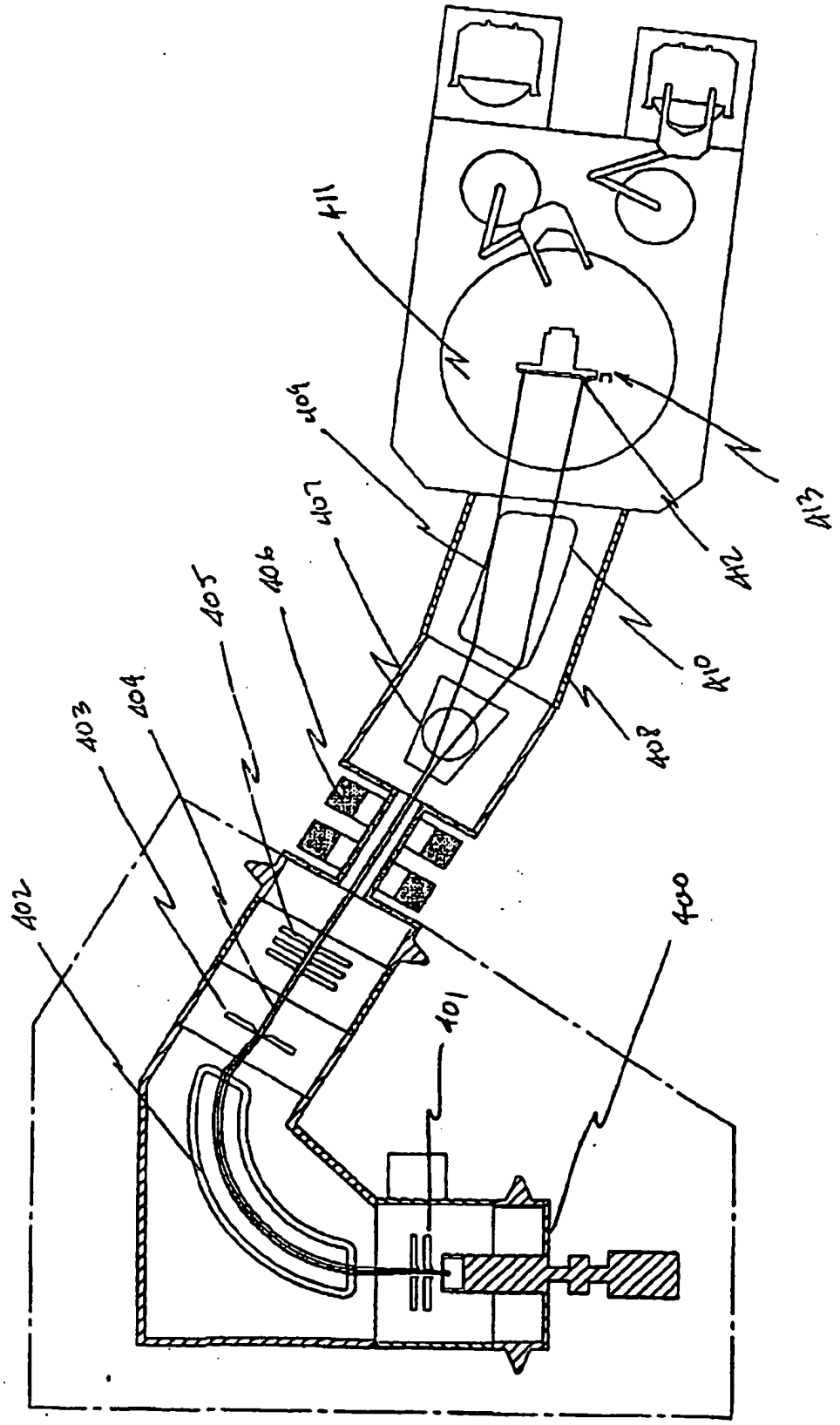


Fig. 1E

10/519699

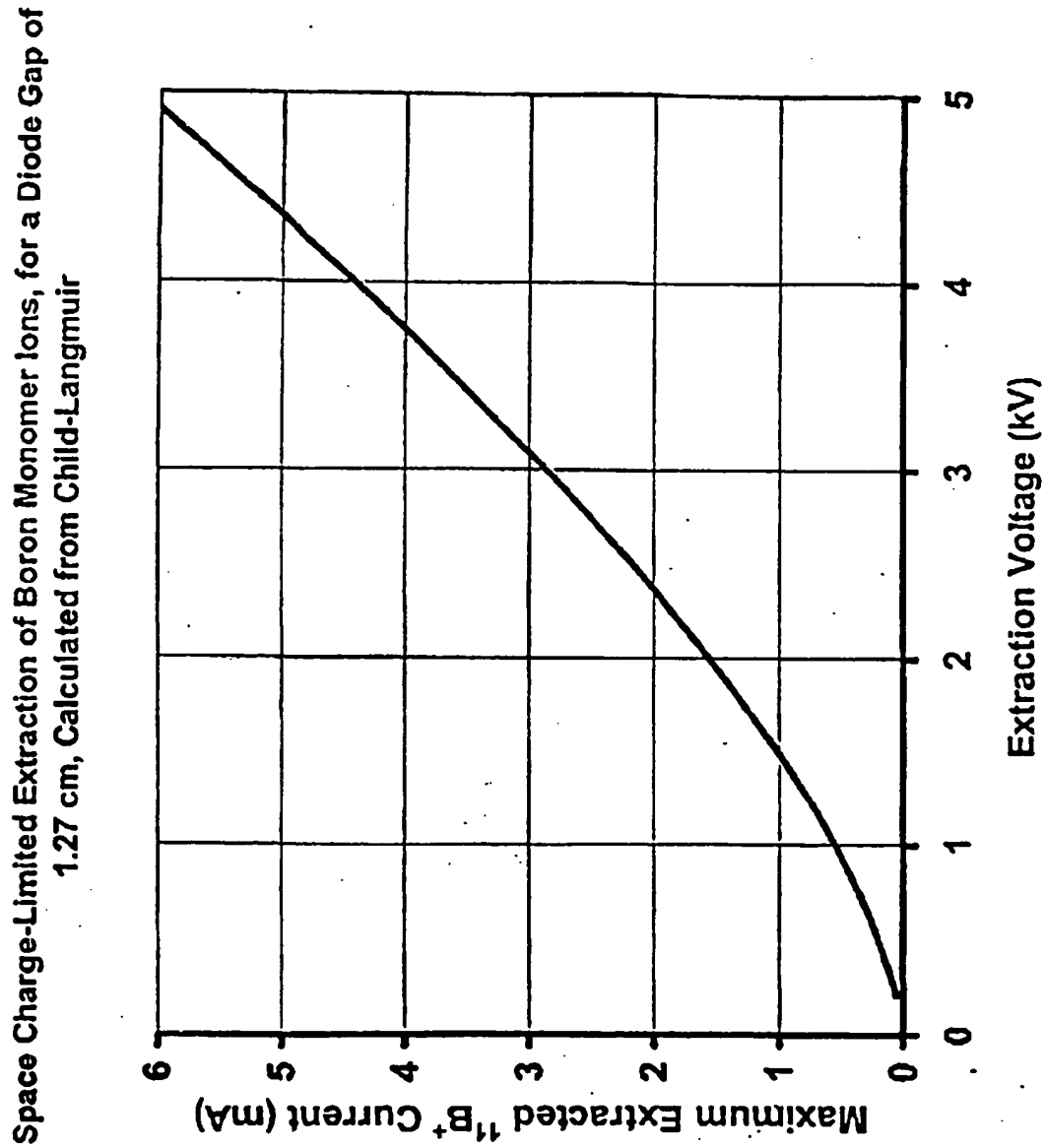
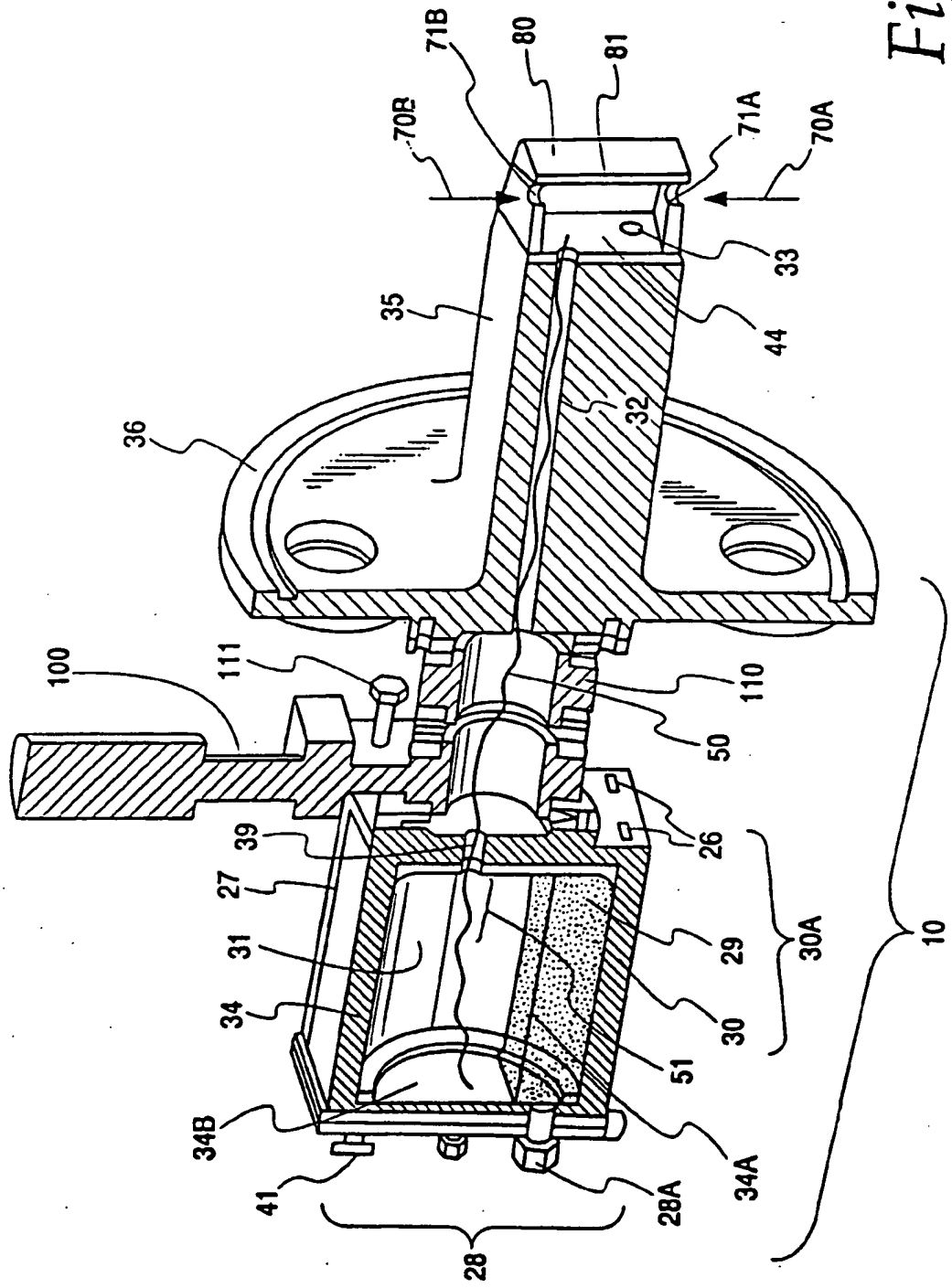


Fig. 2.

10/519699

Fig. 3



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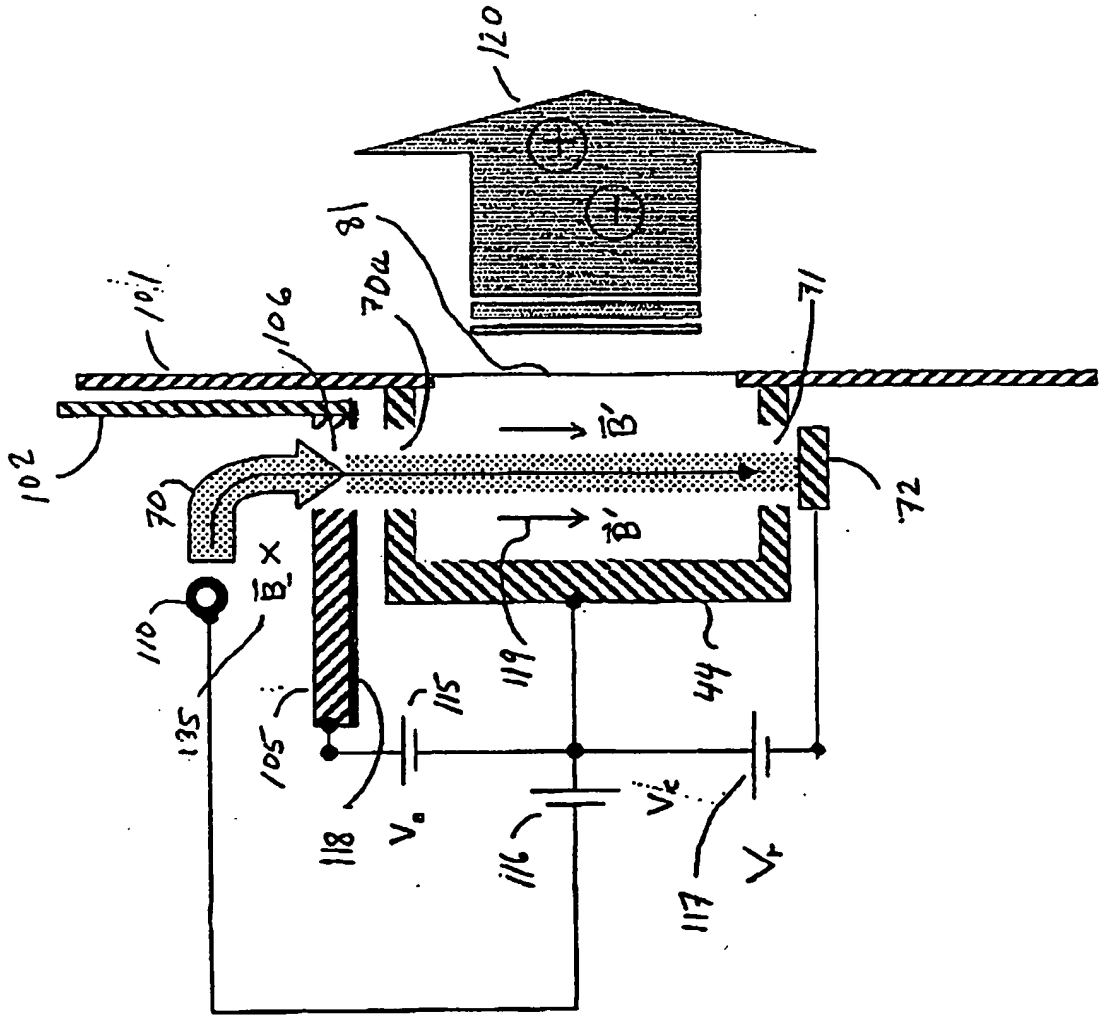


Fig. 4A

10/519699

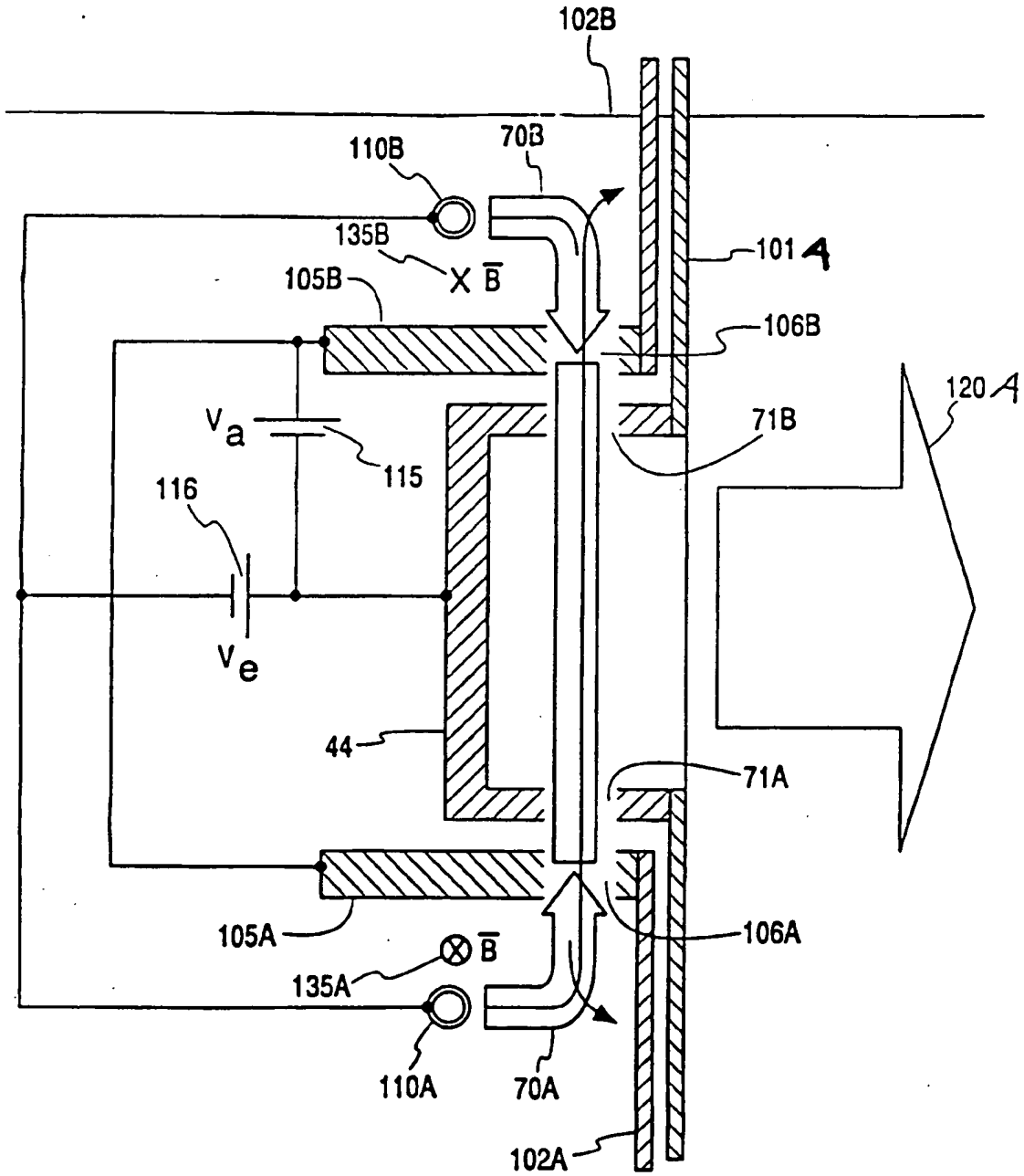


Fig. 4B

10/519699

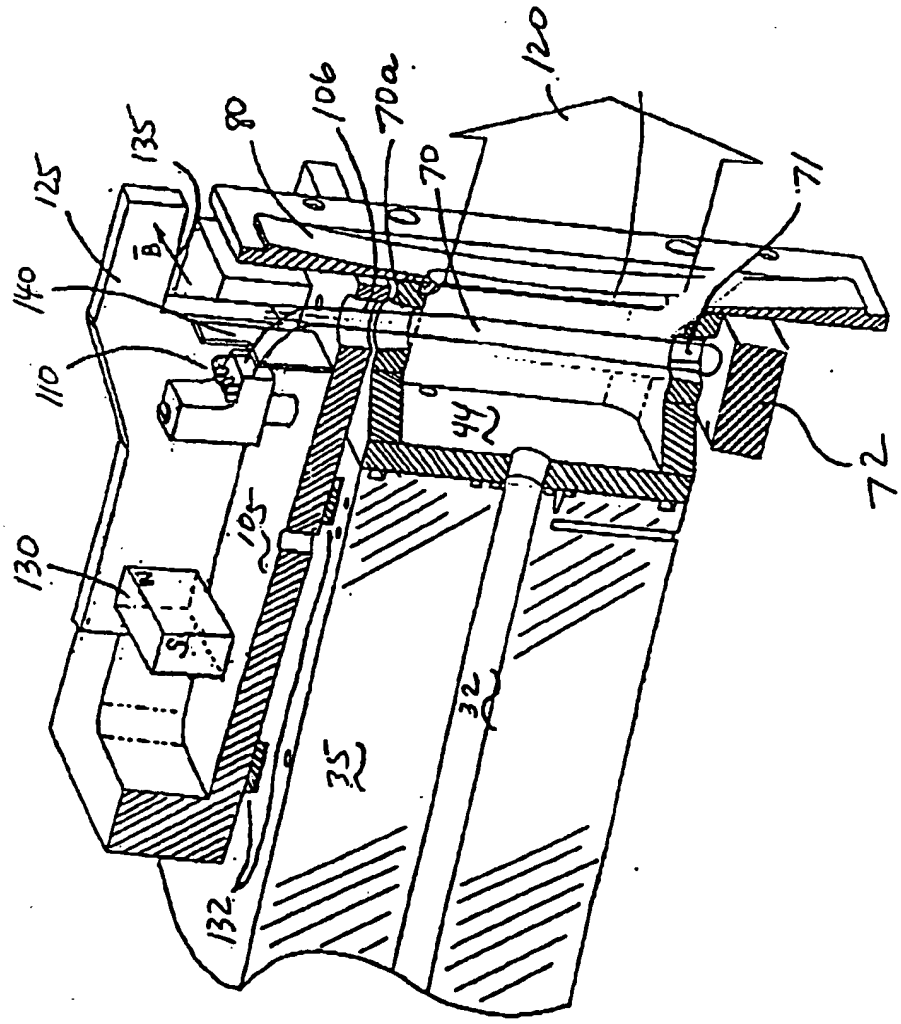
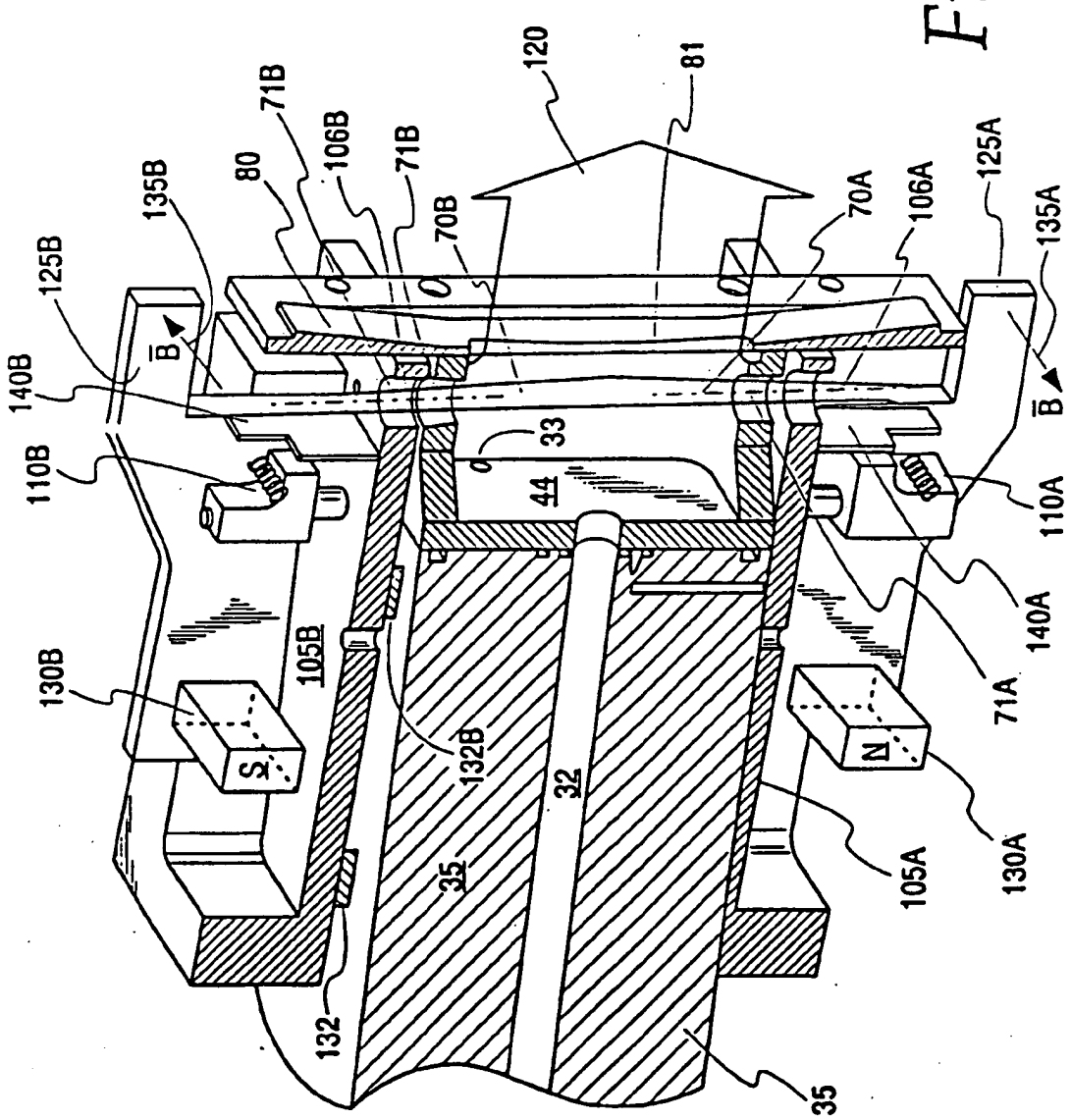


Fig. 5A

10/519699

Fig. 5B



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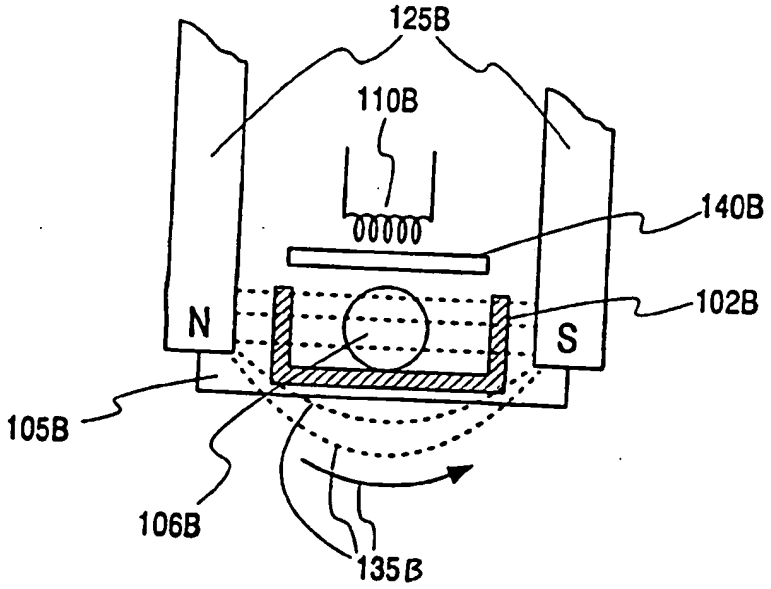

FIG 5c

10/519699

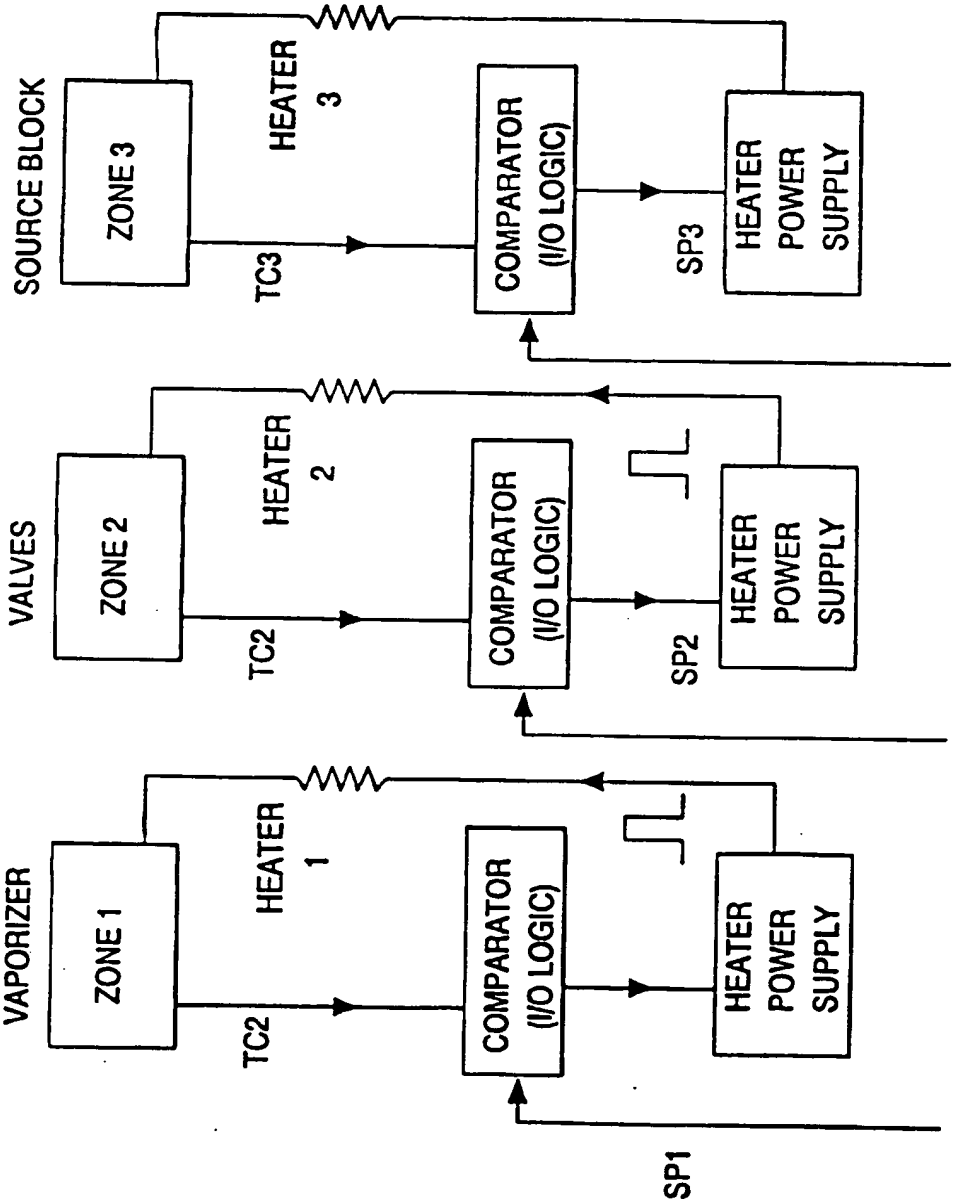

Fig. 6 3-ZONE TEMPERATURE CONTROL SYSTEM

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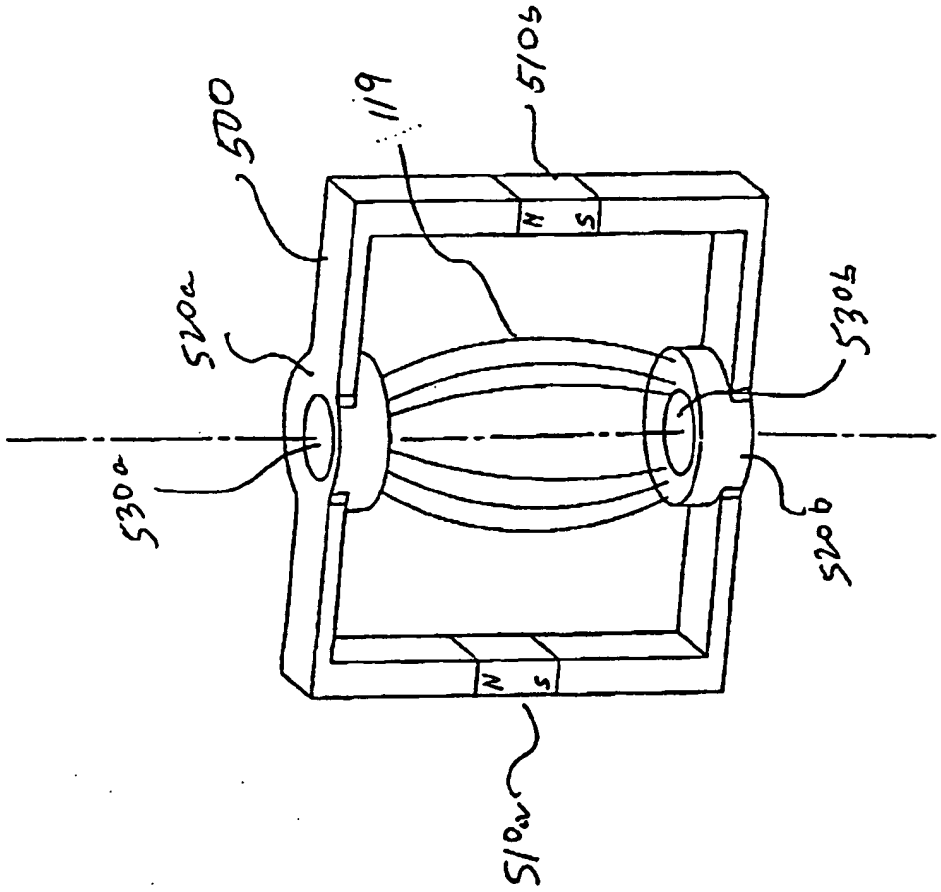

Fig. 7A

10/519699

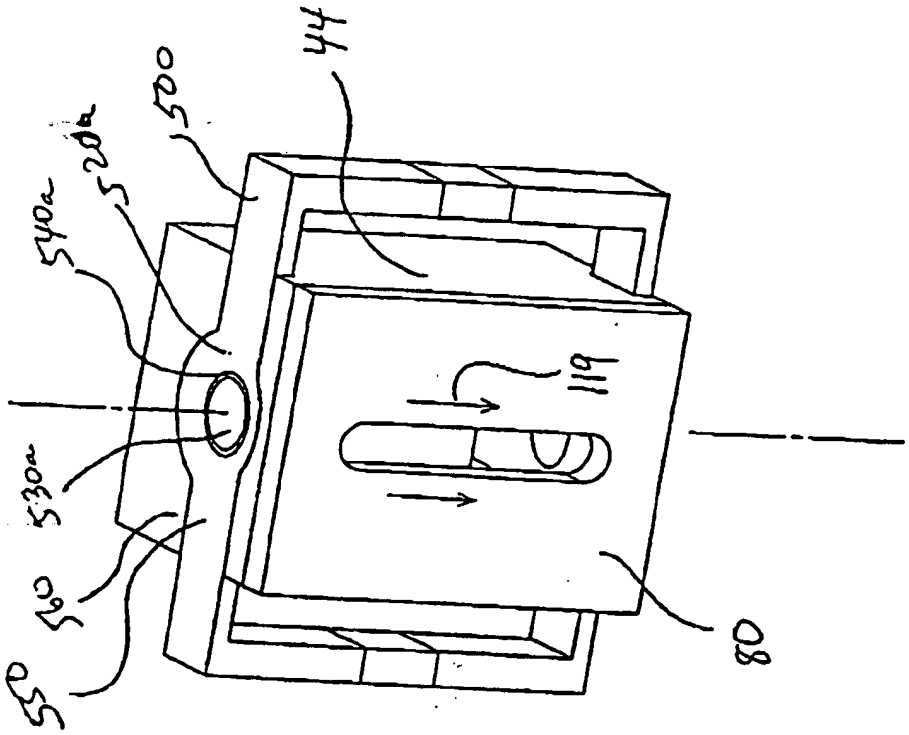

Fig 7B

10/519699

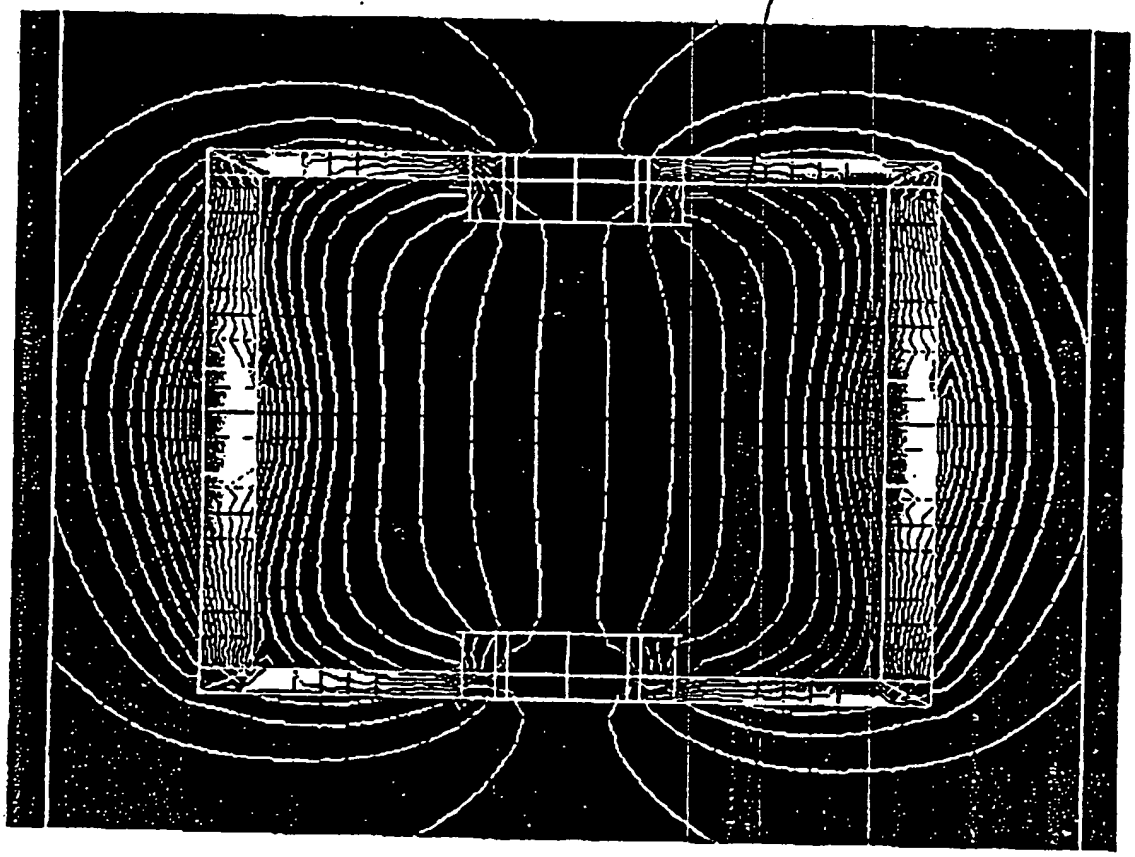

Fig 7c

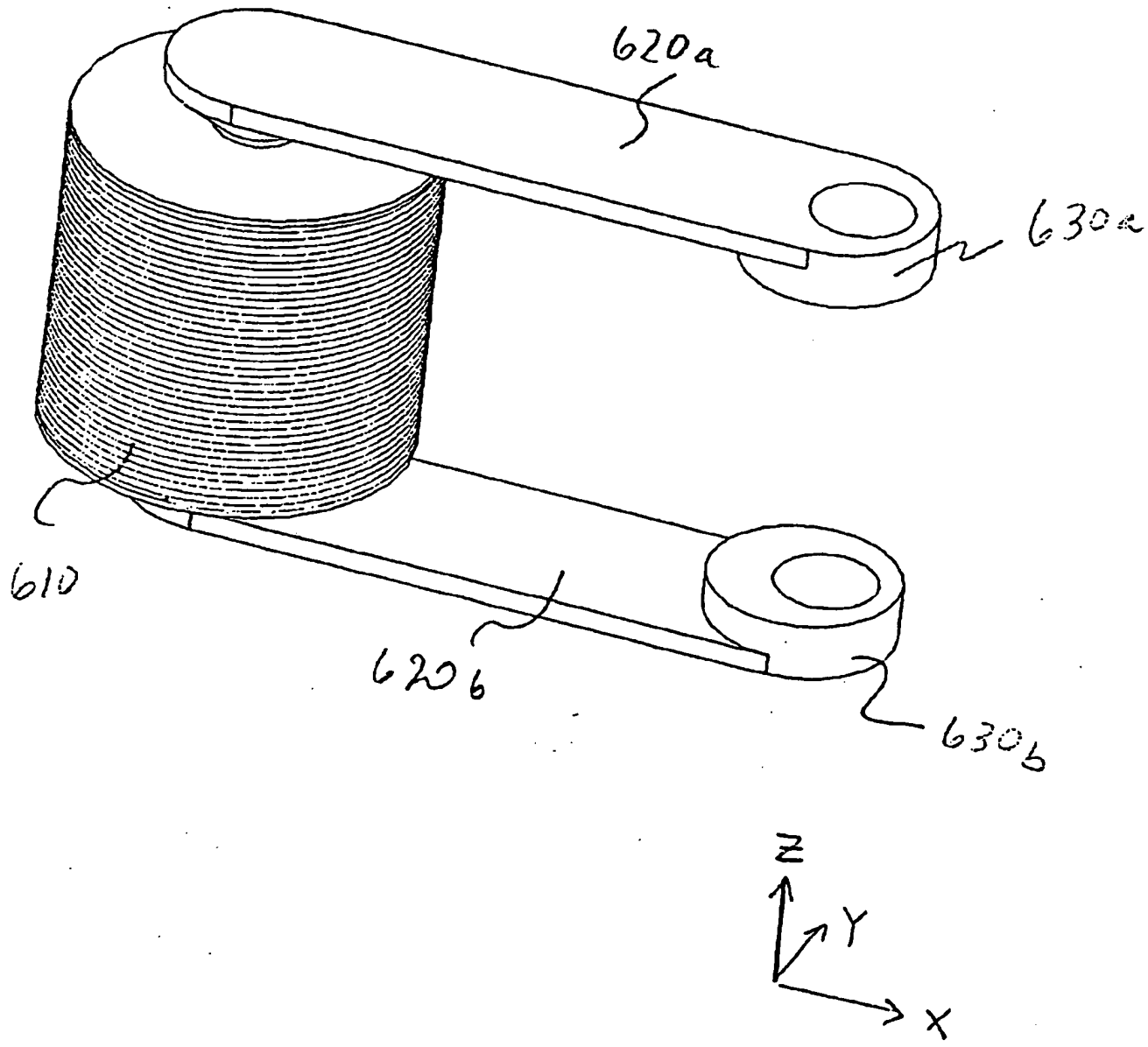

Fig. 70

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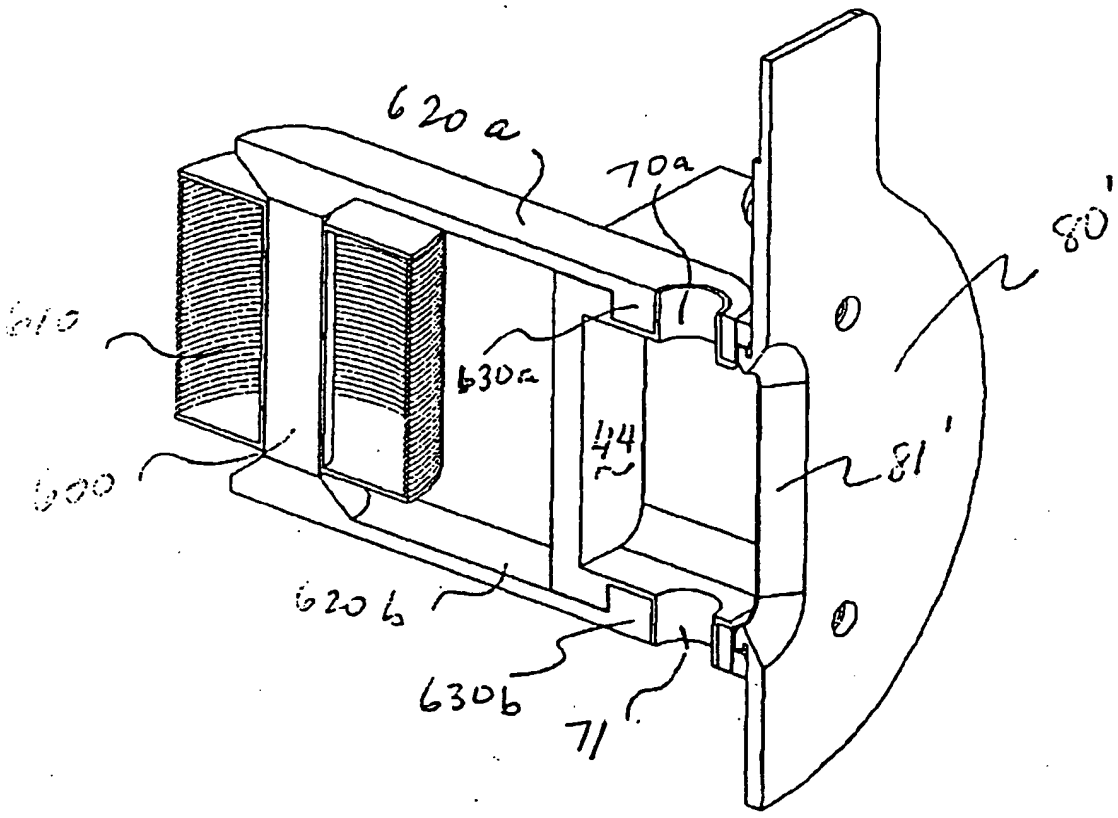

Fig. 7E

10/519699

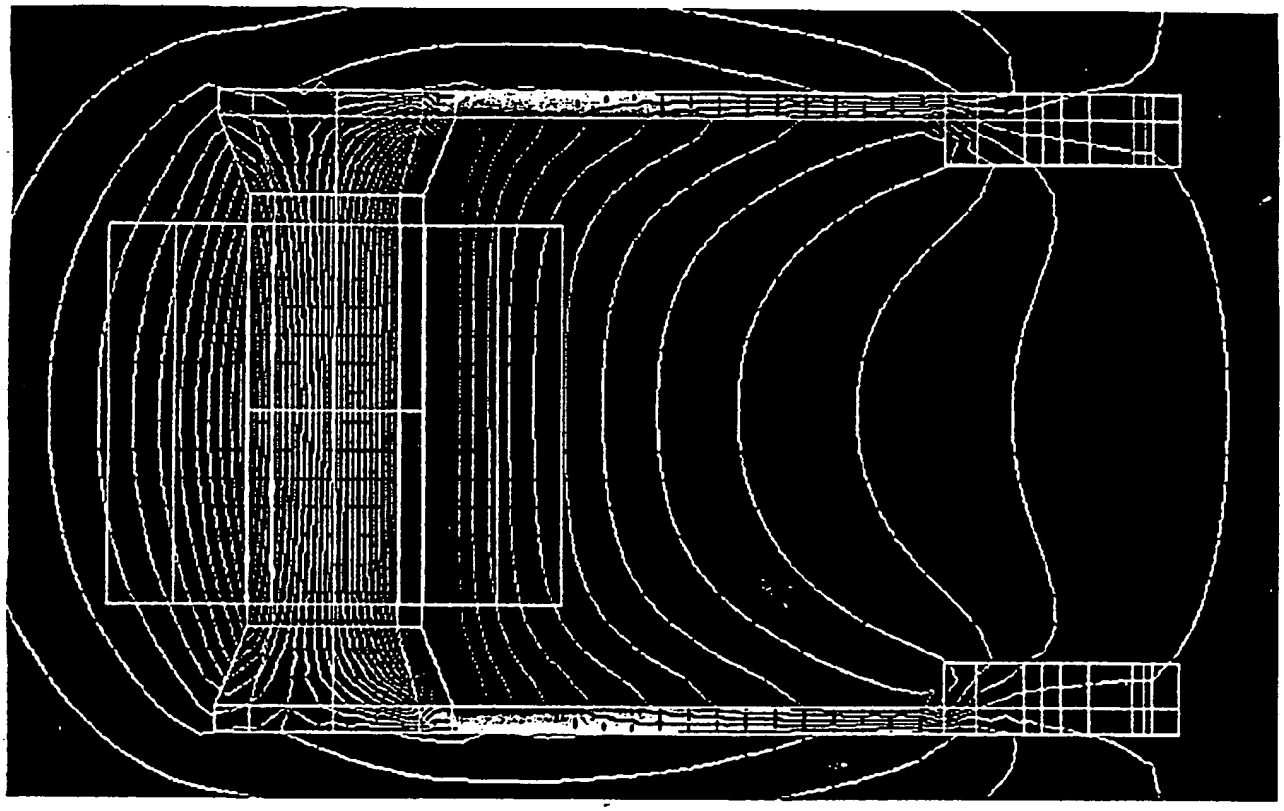

Fig. 7F

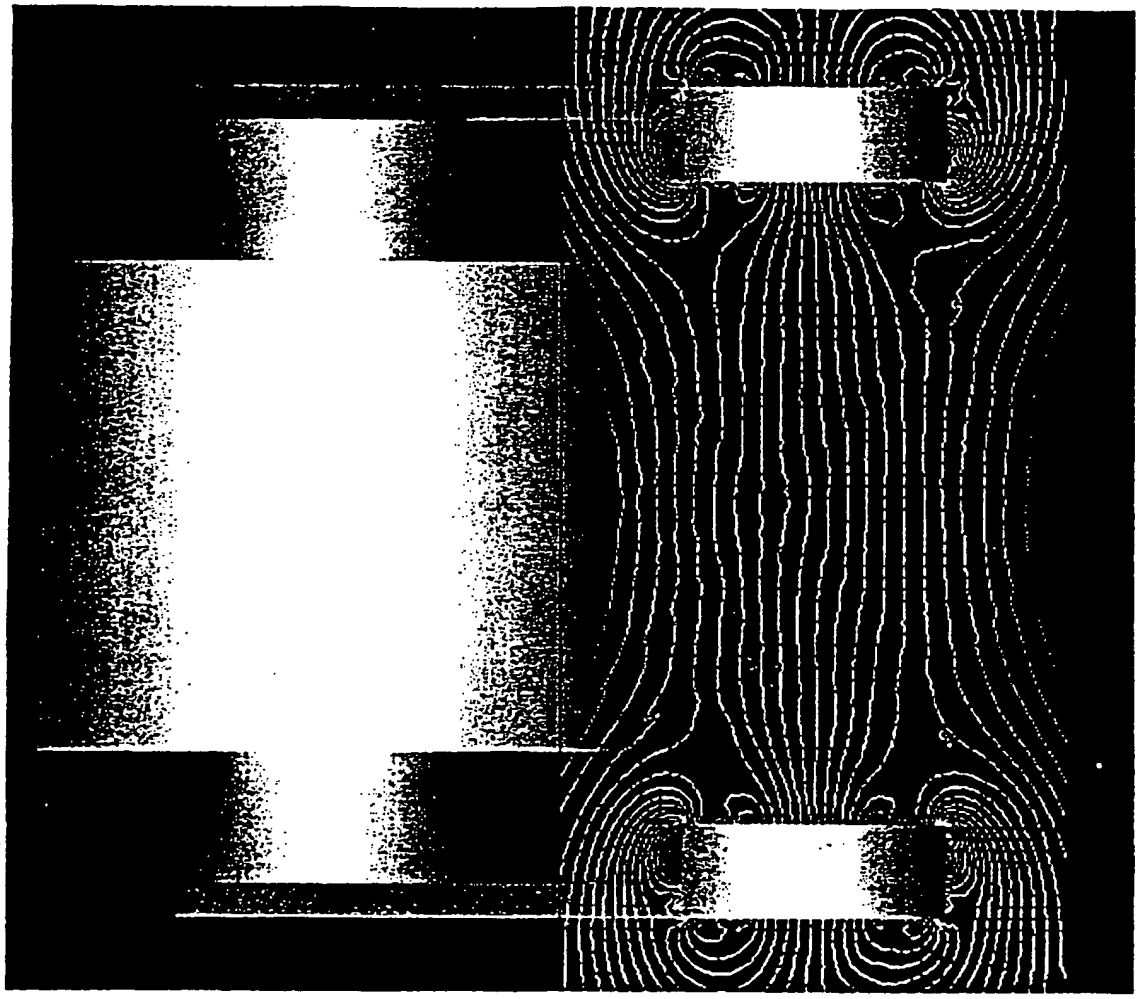

Fig. 7G

10/519699

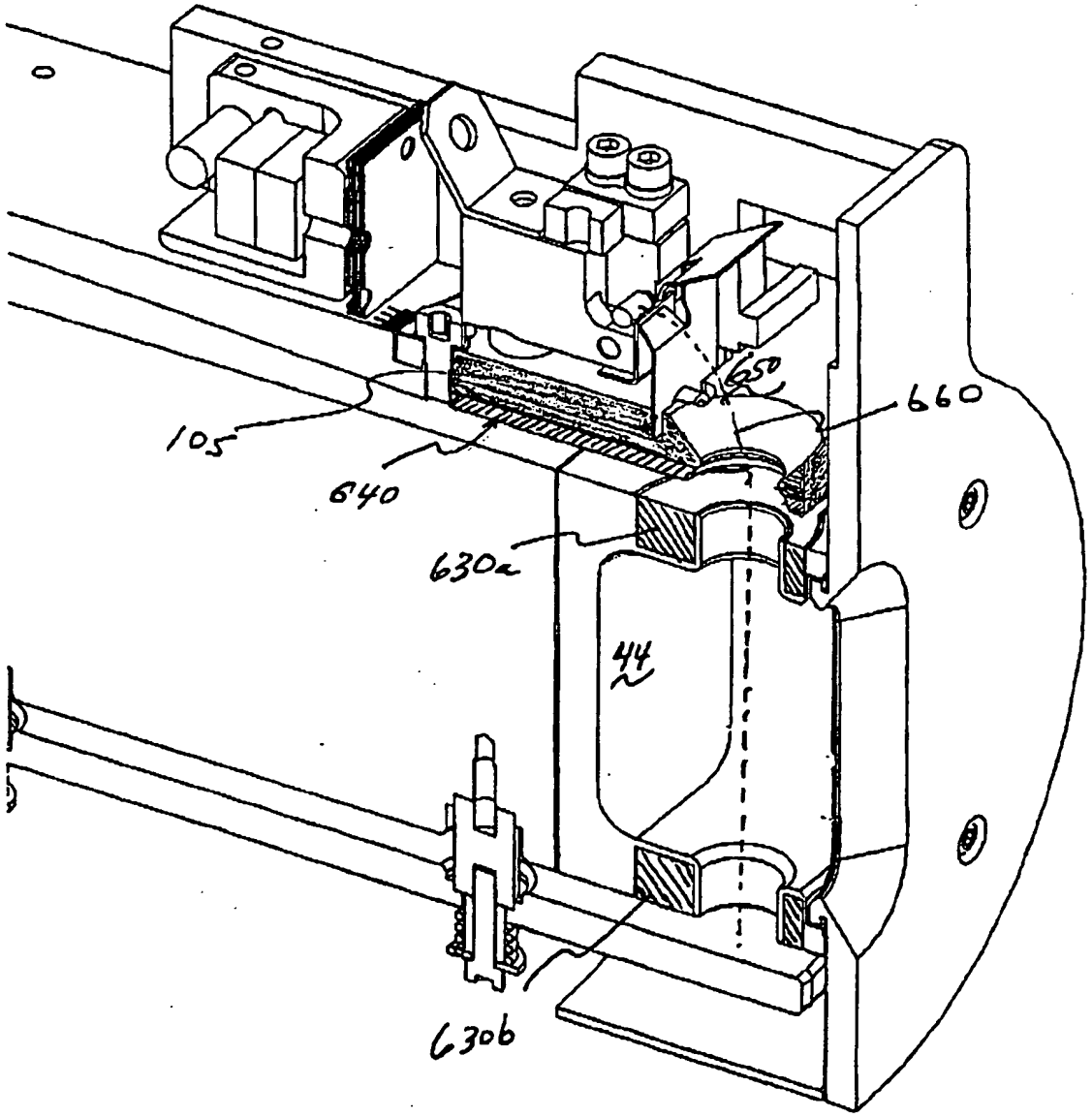

Fig. 7H

10/519699

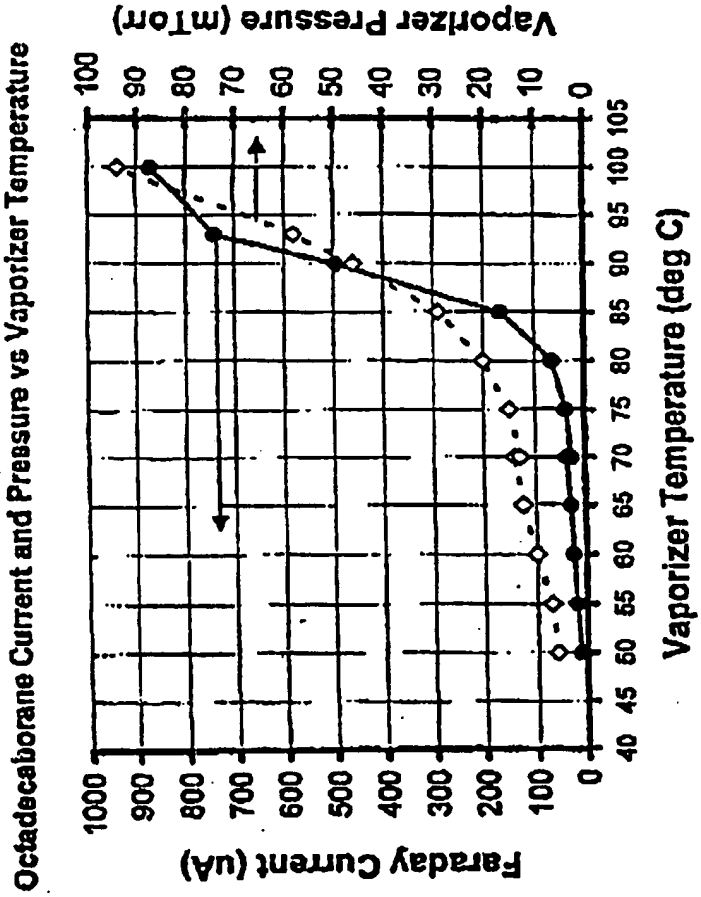

Fig. 8A

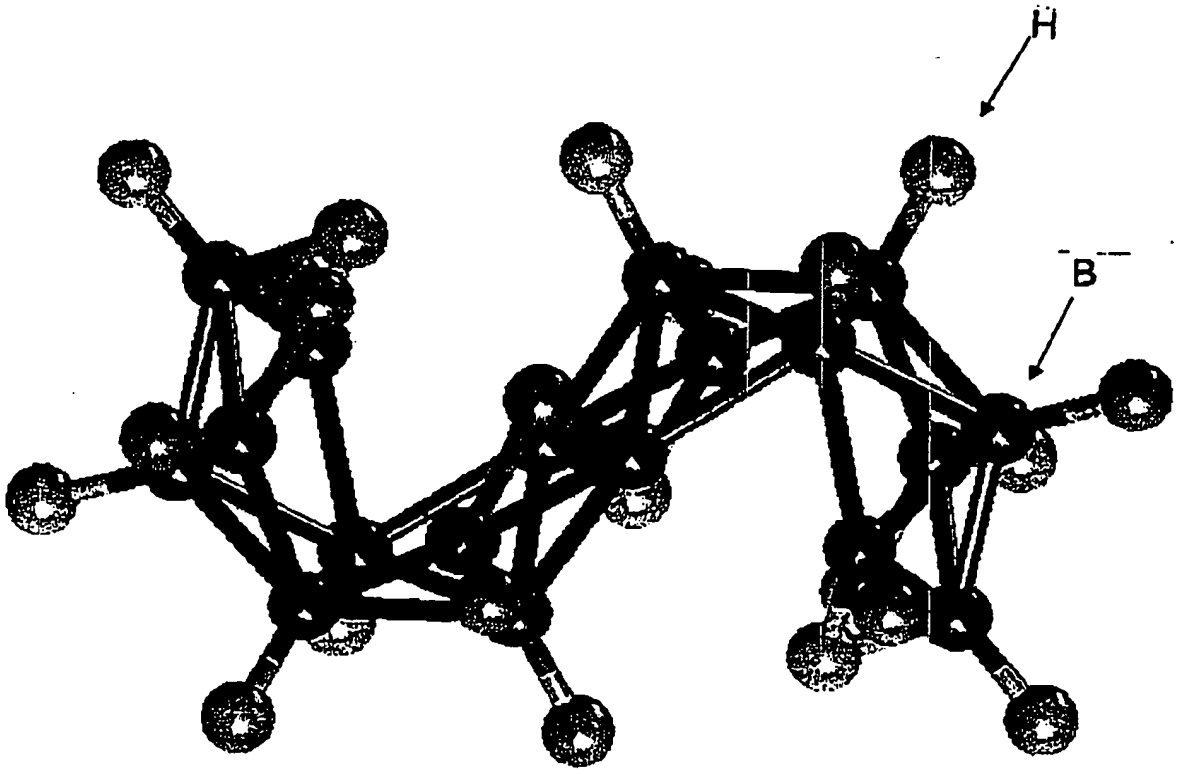

Fig. 8b Octadecaborane ($B_{18}H_{22}$) Molecule.

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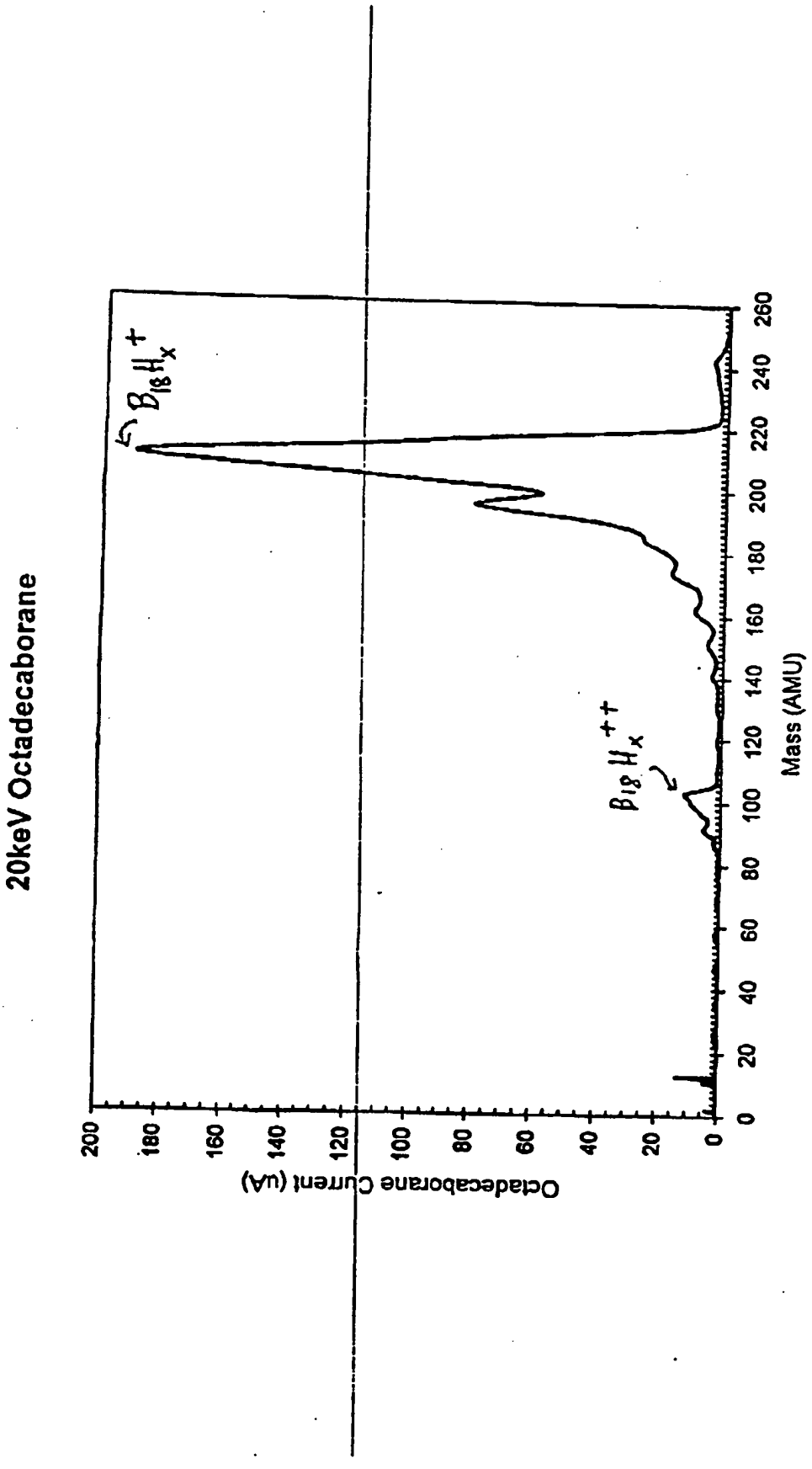

FIG 9

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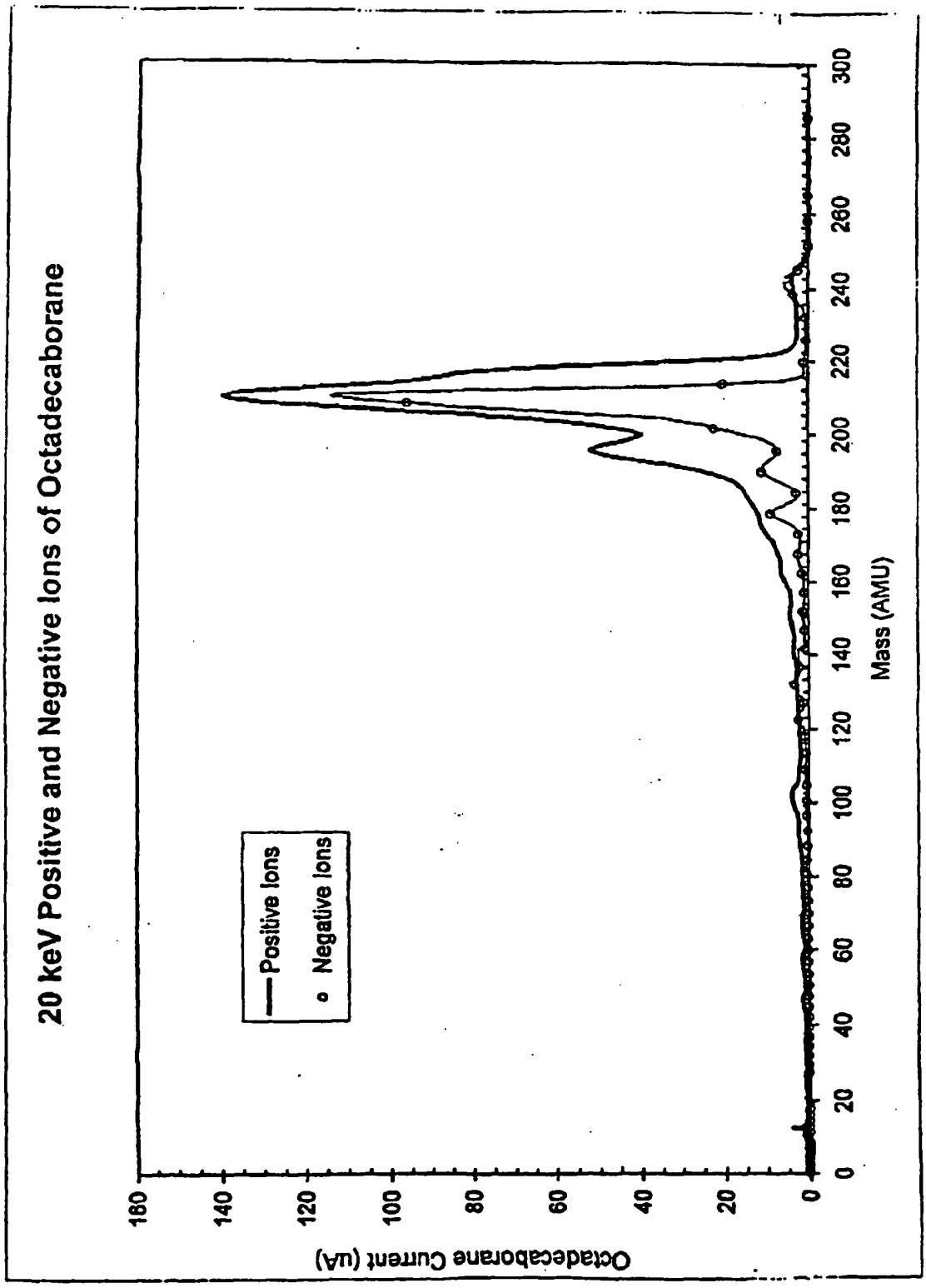

Fig. 10

10/519699

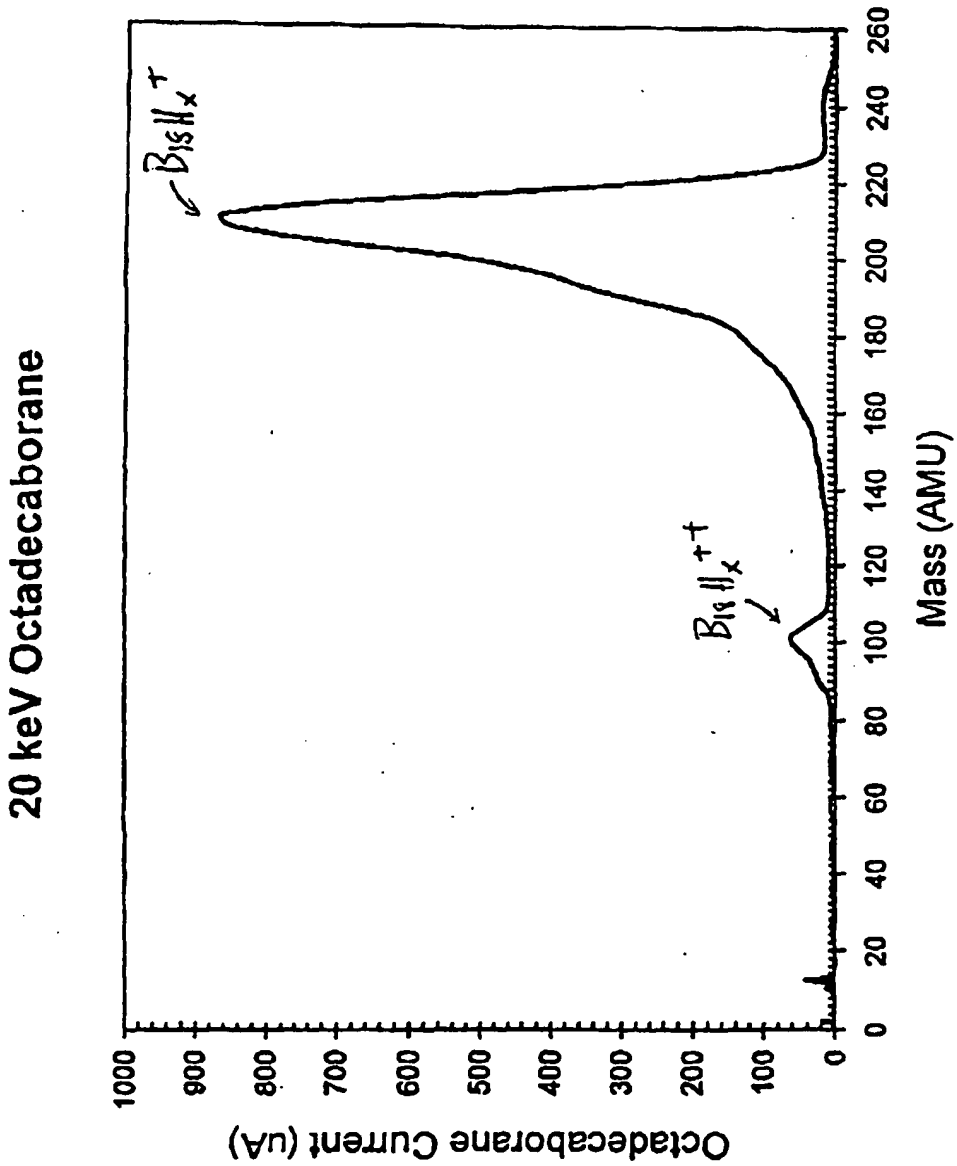

Fig. 11A

10/519699

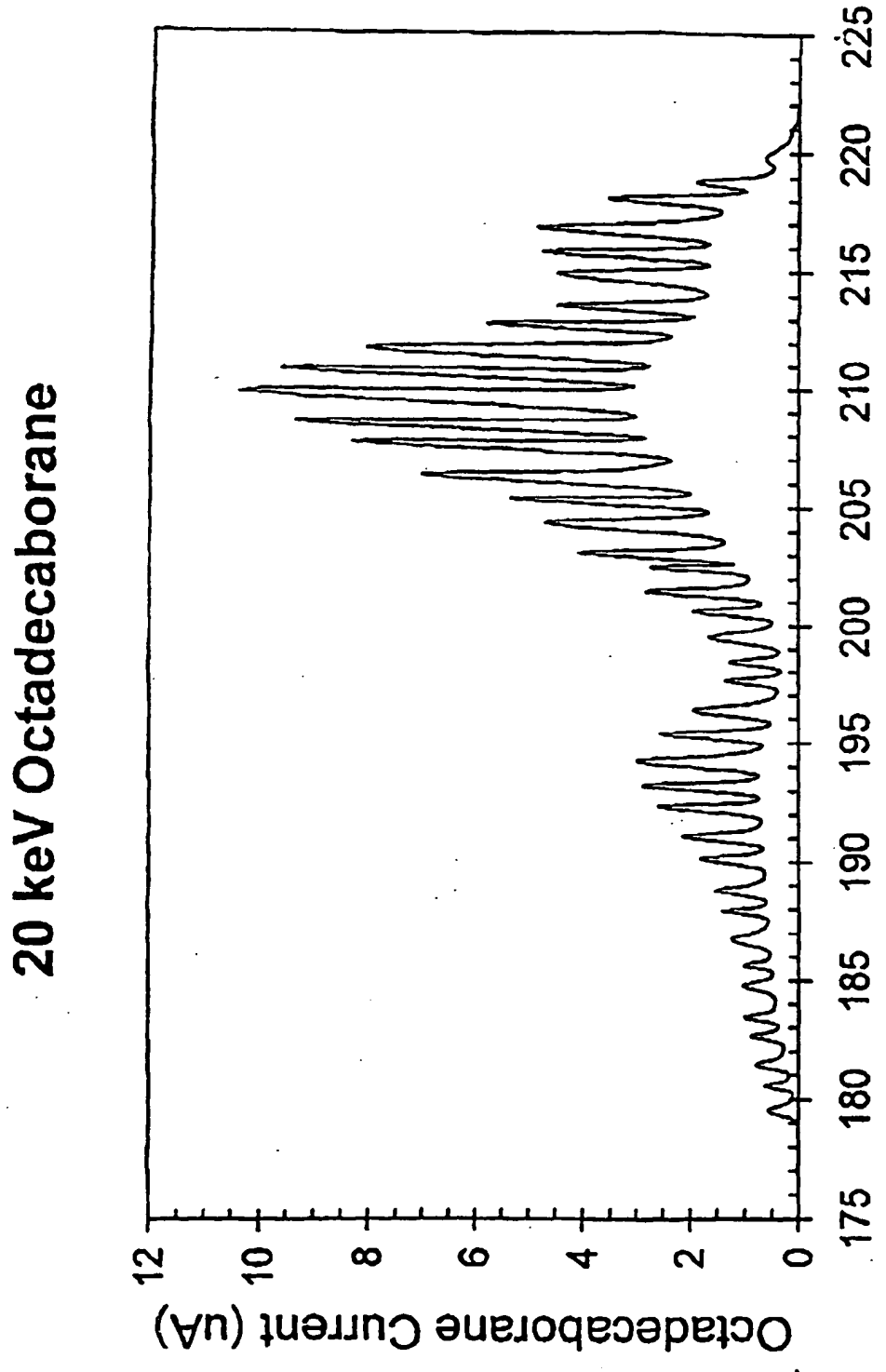

Fig. 11B

10/519699

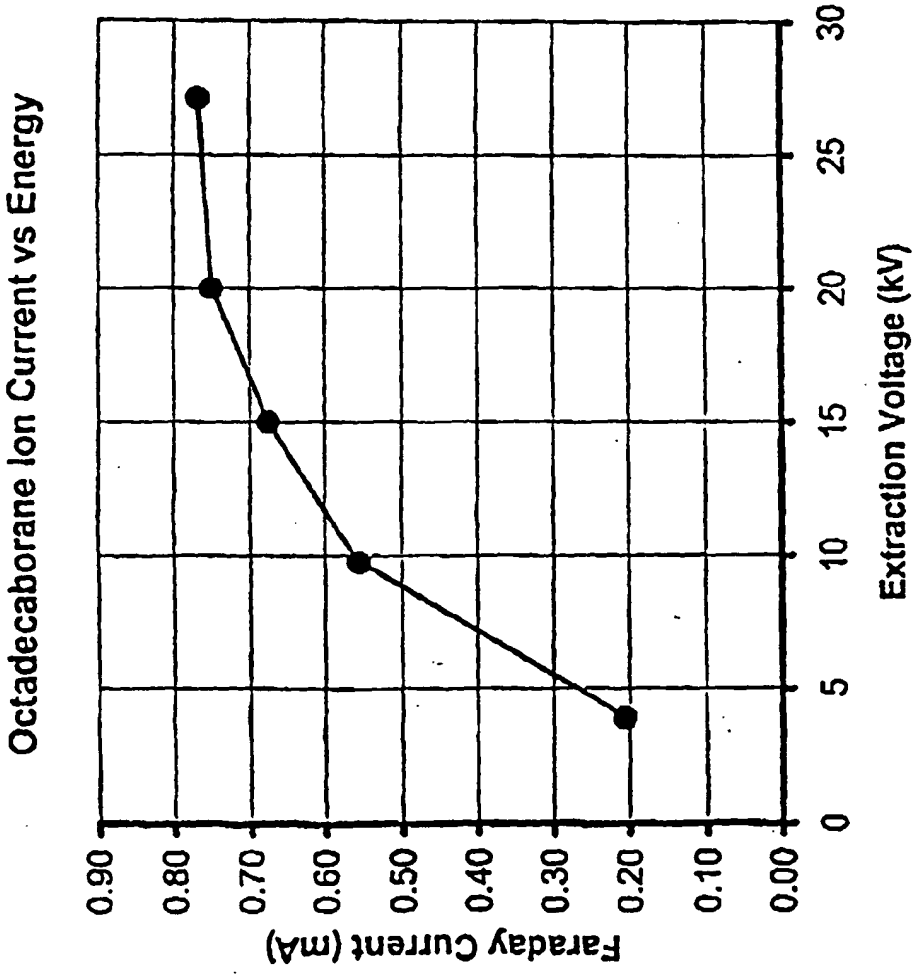

Fig. 12

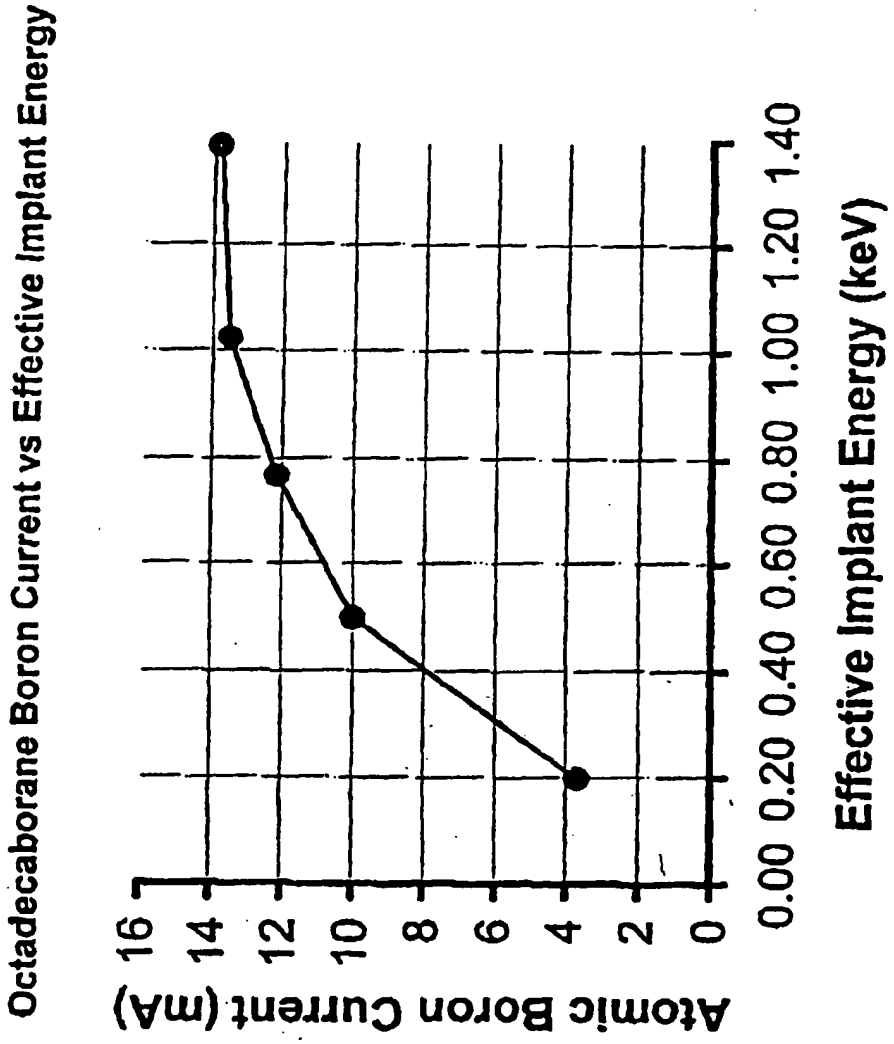
Octadecaborane Boron Current vs Effective Implant Energy
Atomic Boron Current (mA)
16
14
12
10
8
6
4
2
0
0.00 0.20 0.40 0.60 0.80 1.00 1.20 1.40
Effective Implant Energy (keV)

Fig. 13

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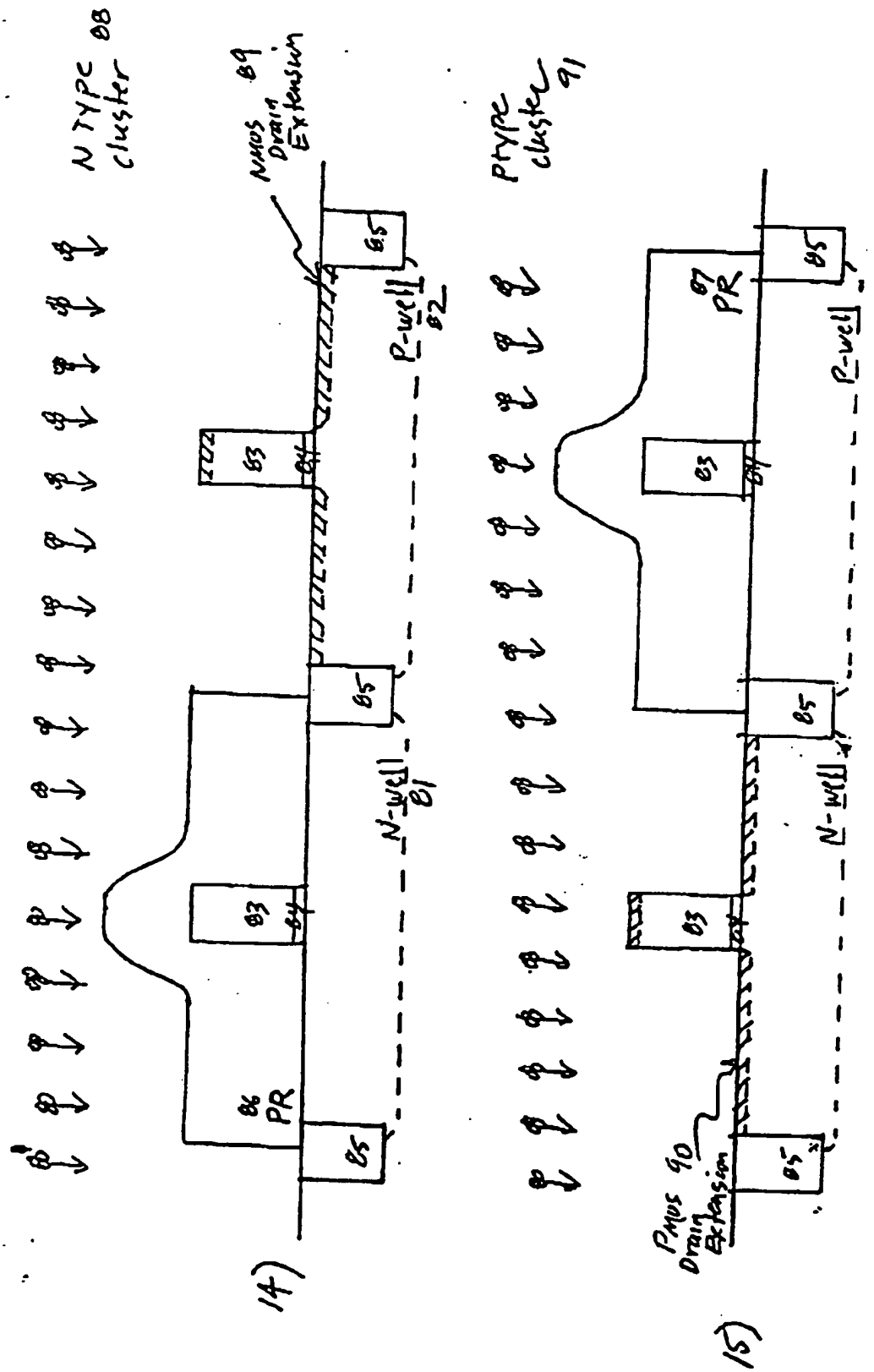

Figs 14, 15: Example of CMOS fabrication sequence 14) NMOS Drain Extension
15) PMOS Drain Extension

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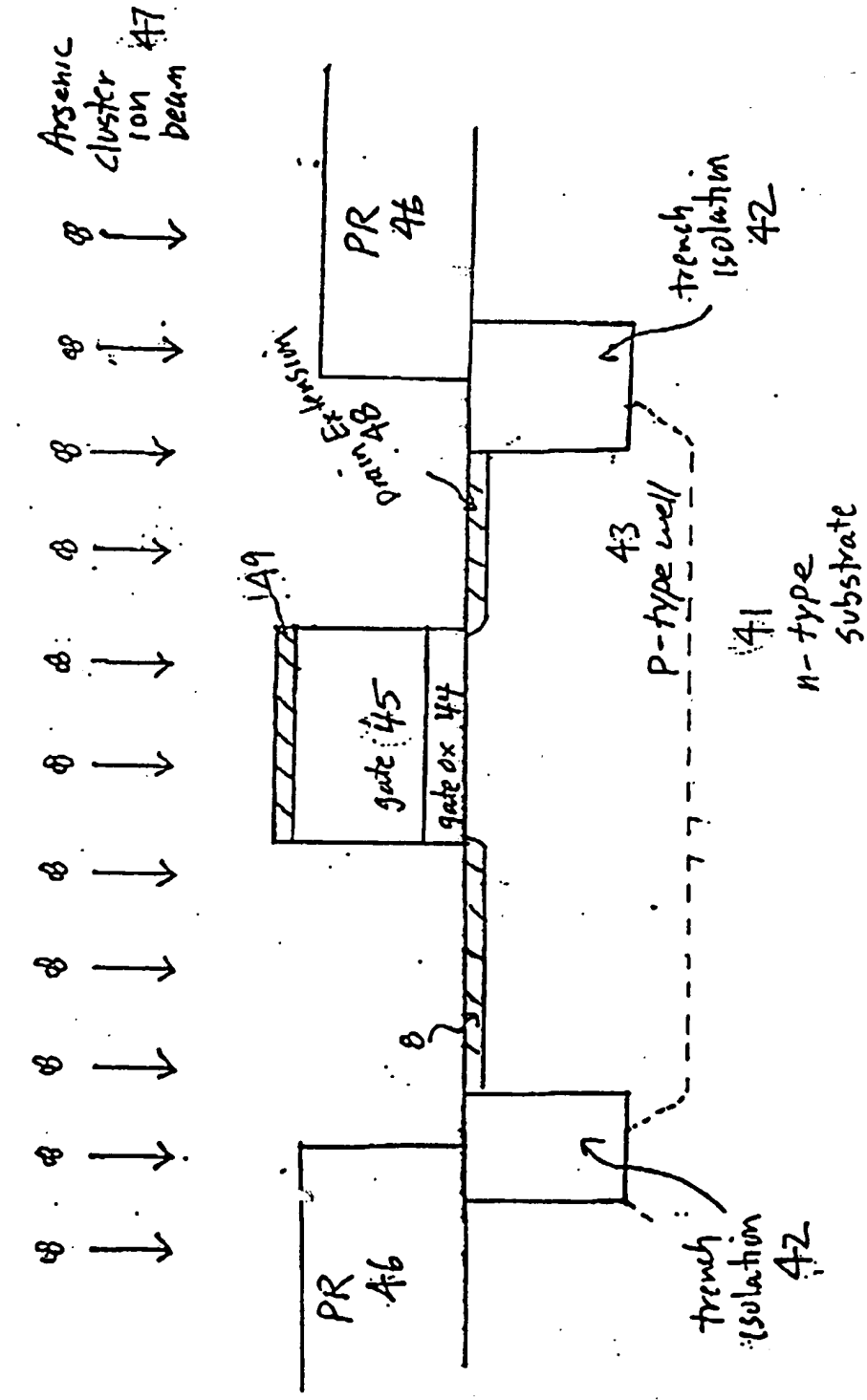


FIG. 16

10/519699

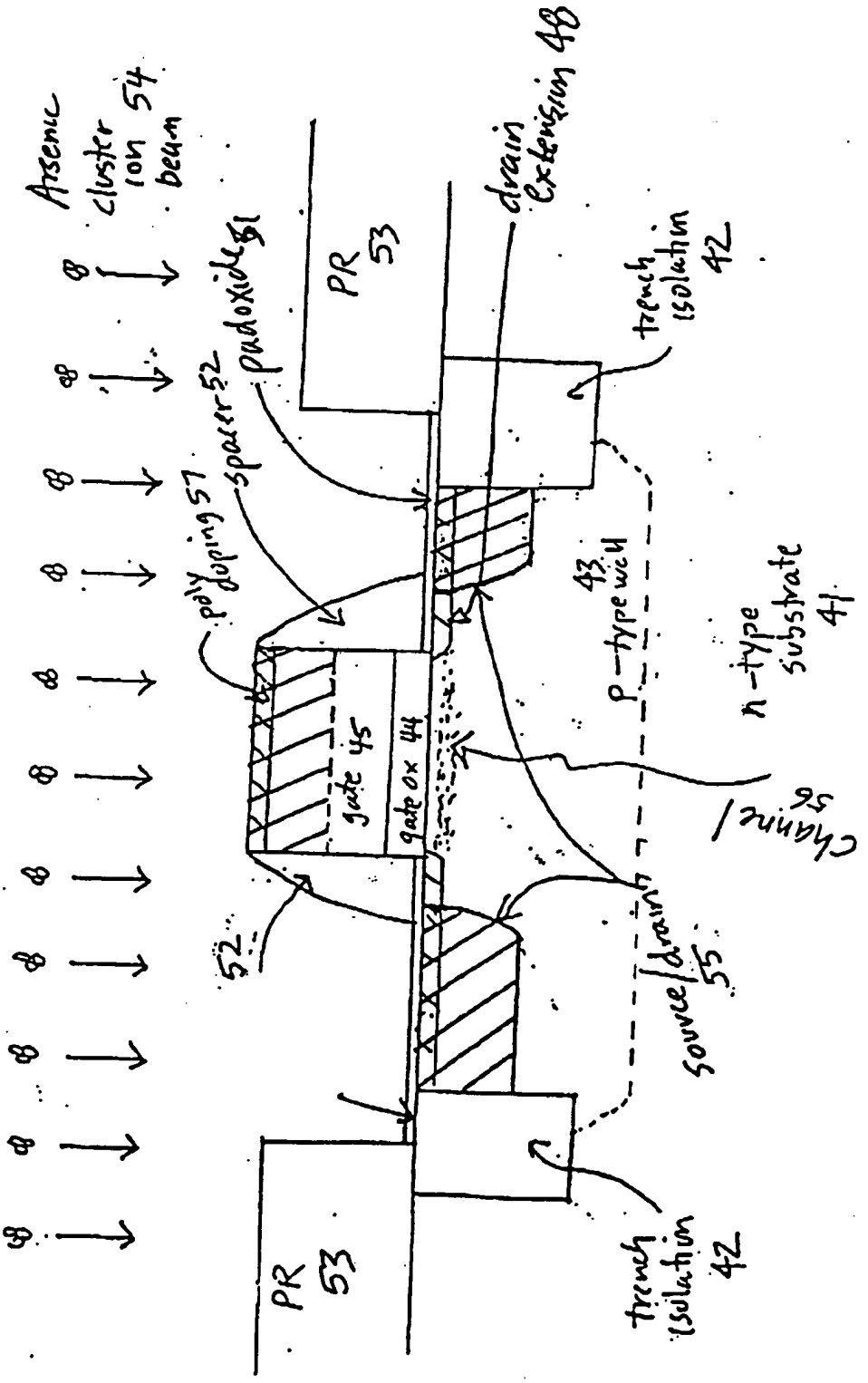


FIG. 17

10/519699

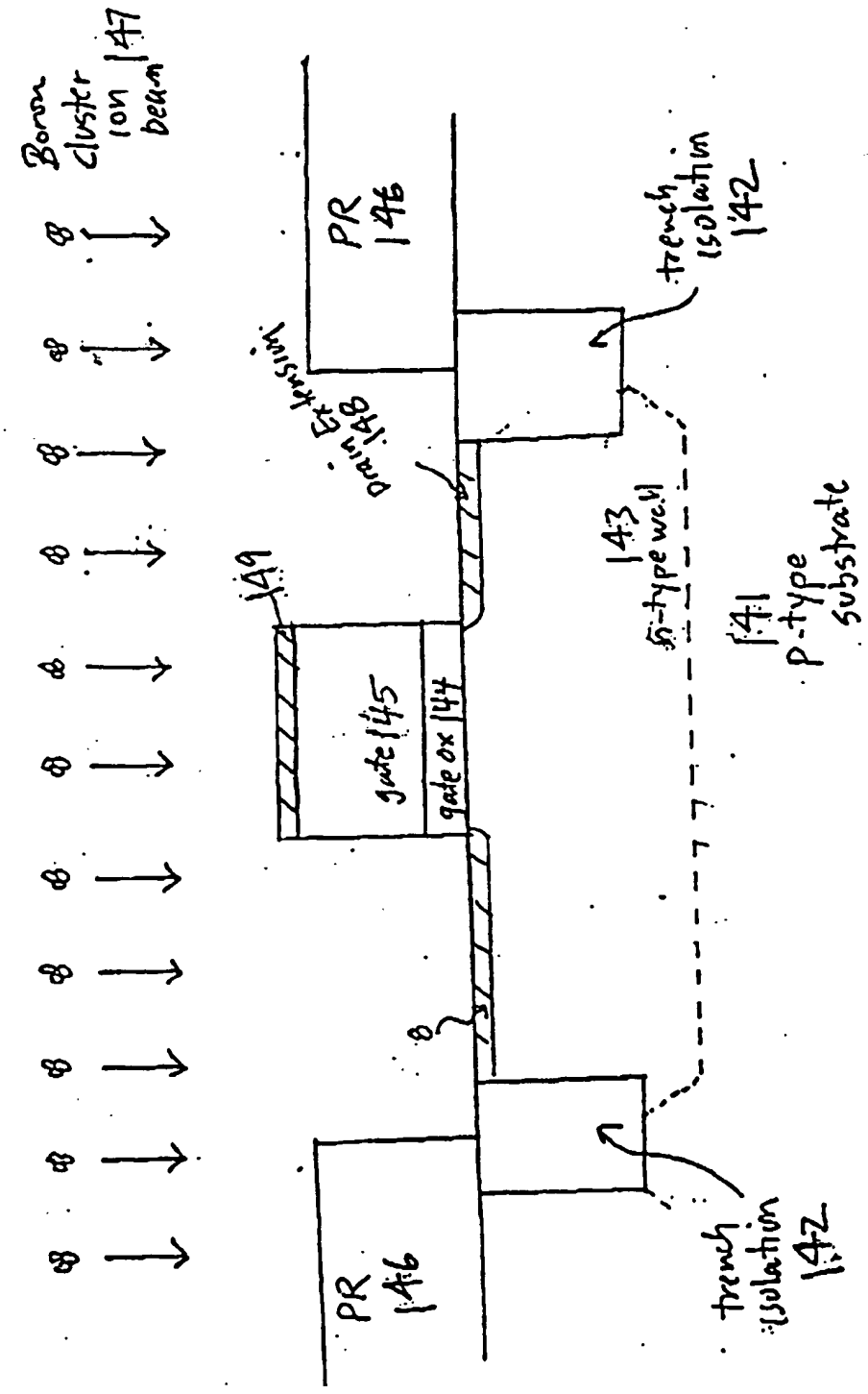


FIG. 18

10/519699

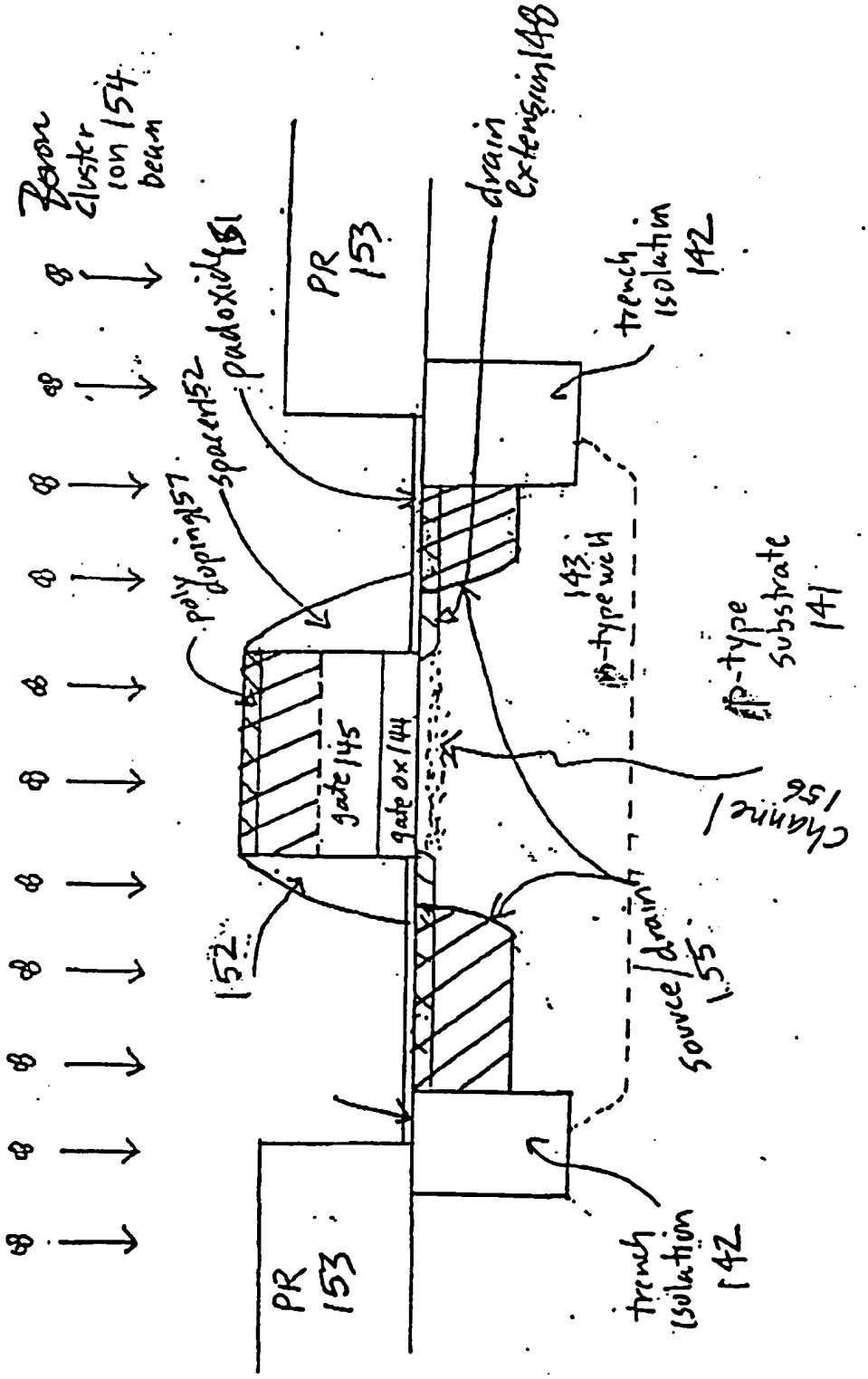


FIG. 19

10/519699

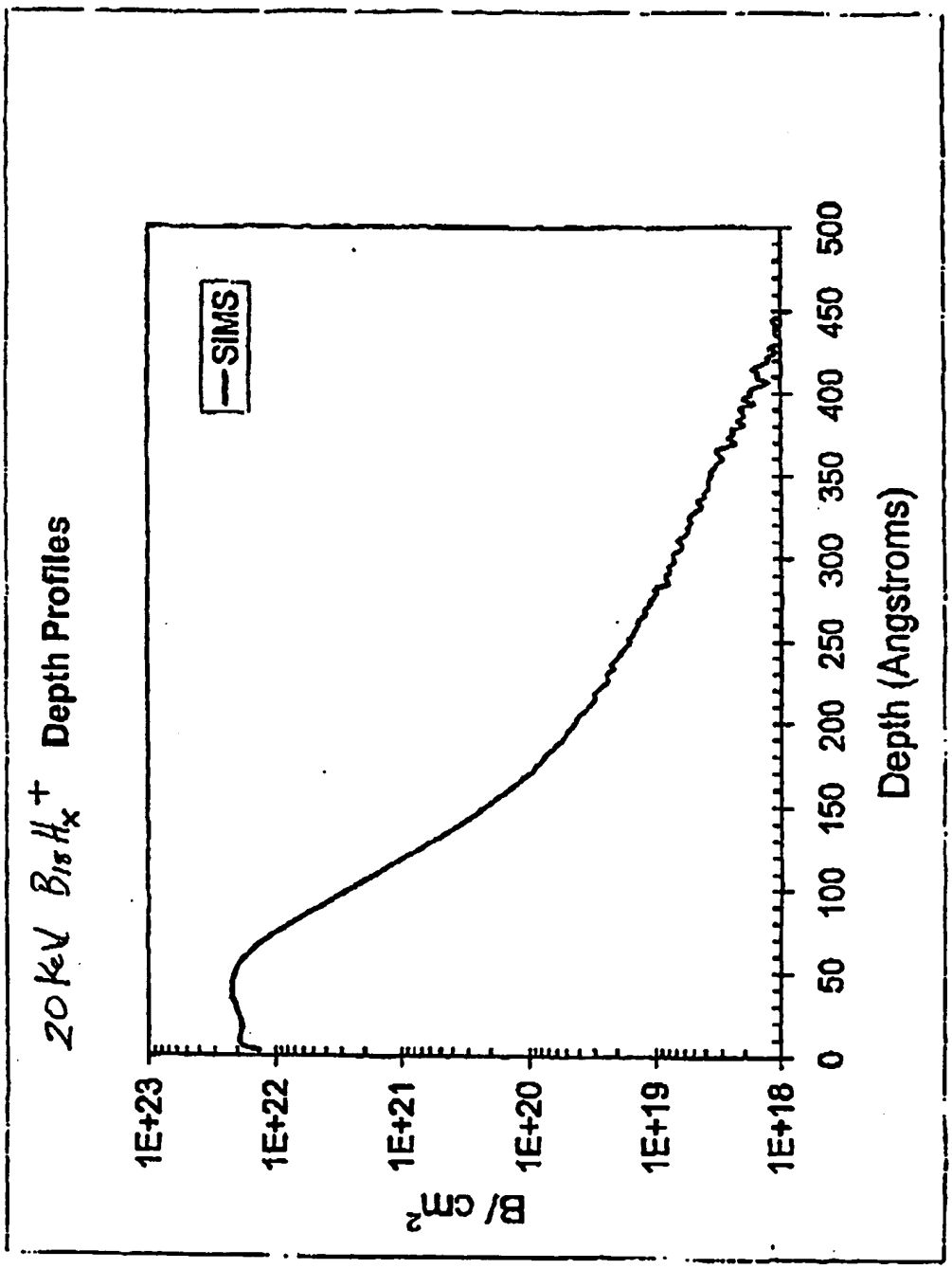
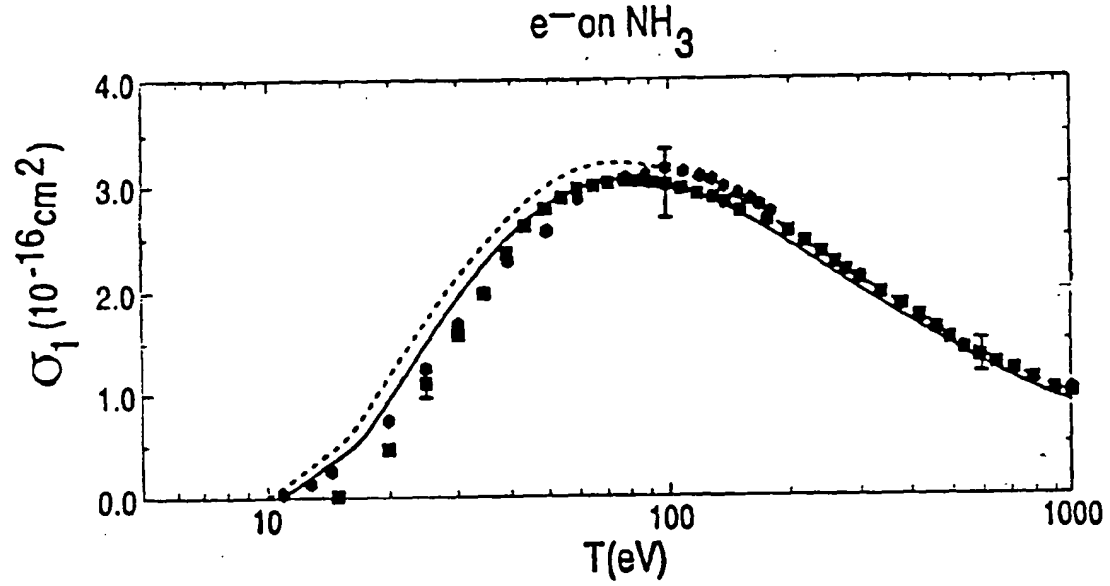


Fig. 20

10/519699



DATA SET	SOURCE
———	BEB (VERTICAL IP) Y.-K. KIM, W. HWANG, N.M. WEINBERGER, M.A. ALI AND M.E. RUDD, J. CHEM. PHYS. 106, 1026 (1997)
- - - - - - - -	BEB (ADIABATIC IP) W. HWANG, Y. -K. KIM AND M.E. RUDD, J. CHEM. PHYS. 104, 2956 (1996).
●	N. DJURIC, D. BELIC, M. KUREPA, J.U. MACK, J. ROTHLEITNER AND T.D. MARK, ABSTRACTS, 12TH INT. CONF ON THE PHYSICS OF ATOMIC AND ELECTRIC COLLISIONS, ED. BY S DATZ (GATLINBURG, 1981), P. 384
■	M.V.V.S. RAO AND S.K. SRIVASTAVA, J. PHYS. B 25,2175 (1992)

FIG 21